

Future Information Processing: From Nanodevices to Nanosystems

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A Thought System:

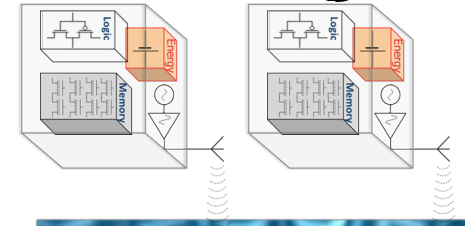
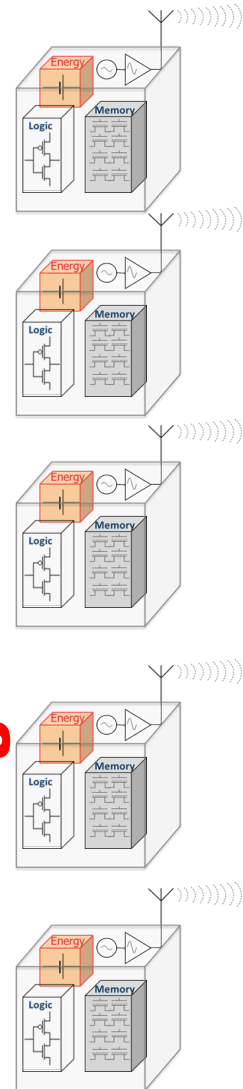
Ultimate Connectivity: Internet of Nanothings

IoT Grand Challenges

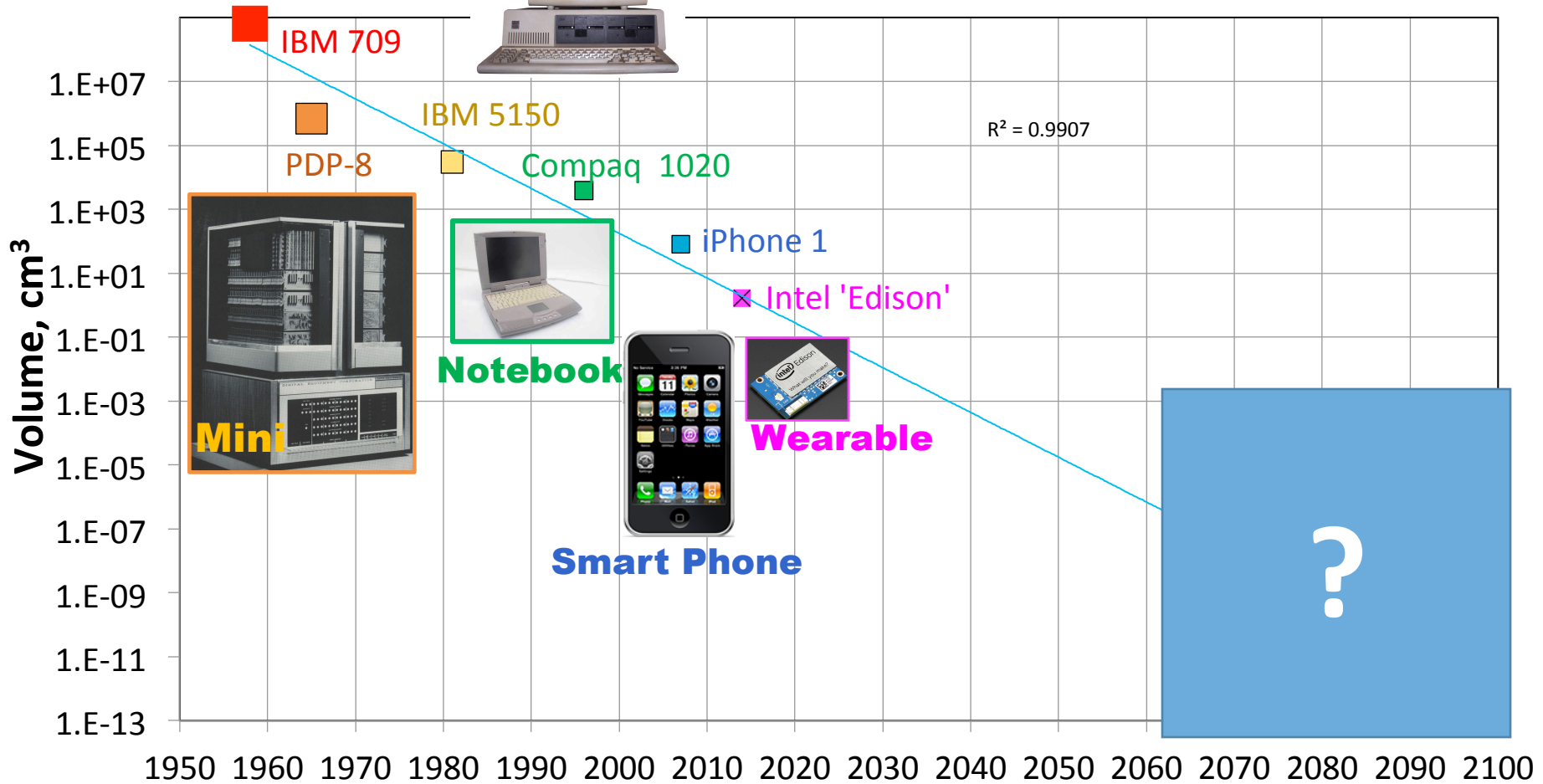
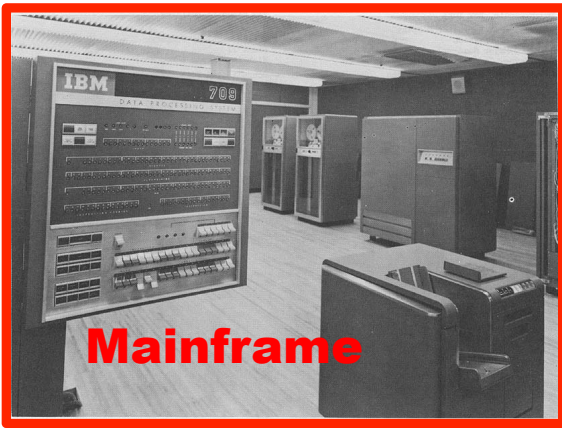
I. Giga-Nano-Tera (Billions of Nanosystems connected in a THz-network)

II. Exa-DataCenters: Semiconductor Technologies for Big Data
(Radically new energy-efficient technologies for storing and analyzing massive volumes of data)

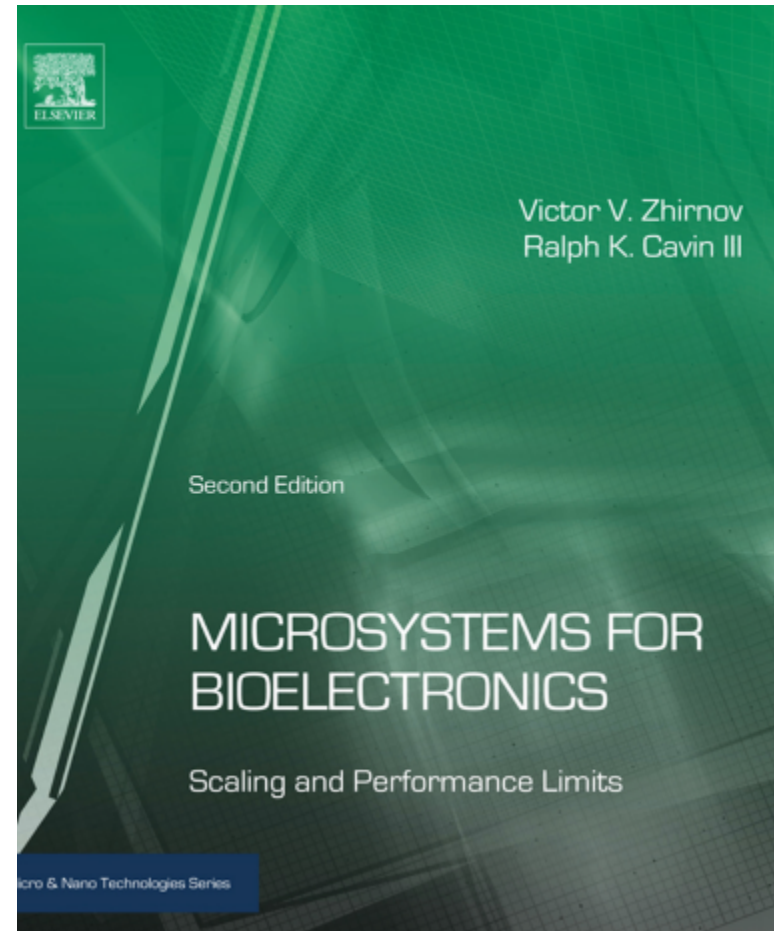
Intelligent NanoNodes



Computing system Scaling (Bell's Law)

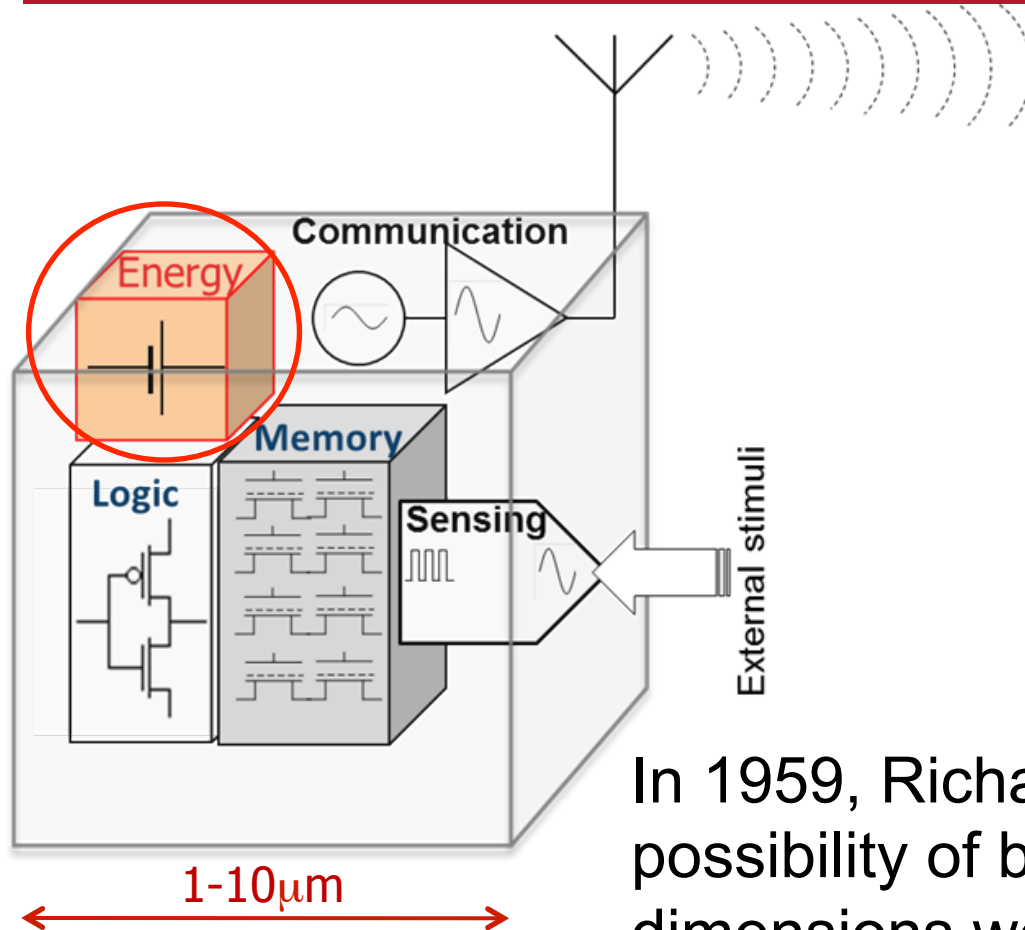


- Physics of extreme scaling of information processing devices and systems
- The connection of device physics and the parameters of the digital circuits
- System's "intelligence" per a volume of matter
- *In Carbo* microsystems: Design Secrets of Nature



Elsevier 2015

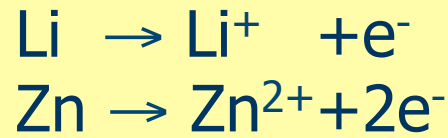
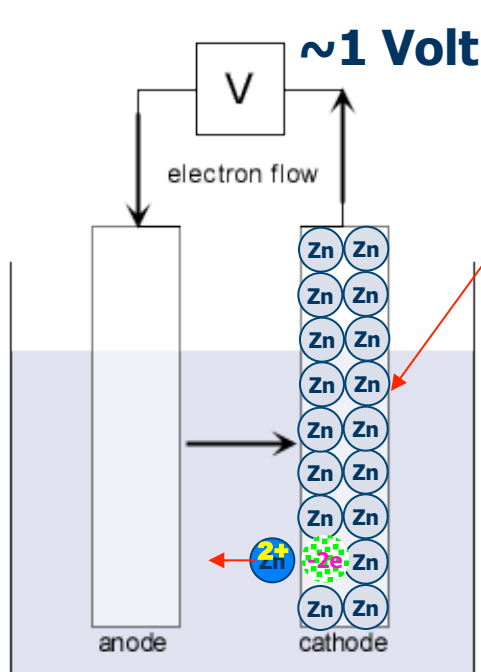
Miniaturizing Limits of a Computer?



In 1959, Richard Feynman suggested the possibility of building computers whose dimensions were 'submicroscopic'. *These submicroscopic computers remain outside of our grasp.*

Energy in the Small

Scaling limits of micro-batteries



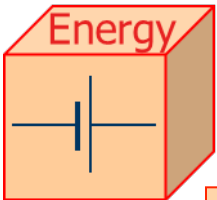
The galvanic cell consumes *atomic fuel* to produce electricity

$\epsilon \sim 1\text{eV/atom}$ (\sim chemical bonding energy)

$$E = \epsilon \cdot N$$

Number of atoms in cathode electrode

The energy output is limited by the *Avogadro's number, N_A*

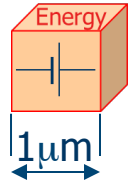


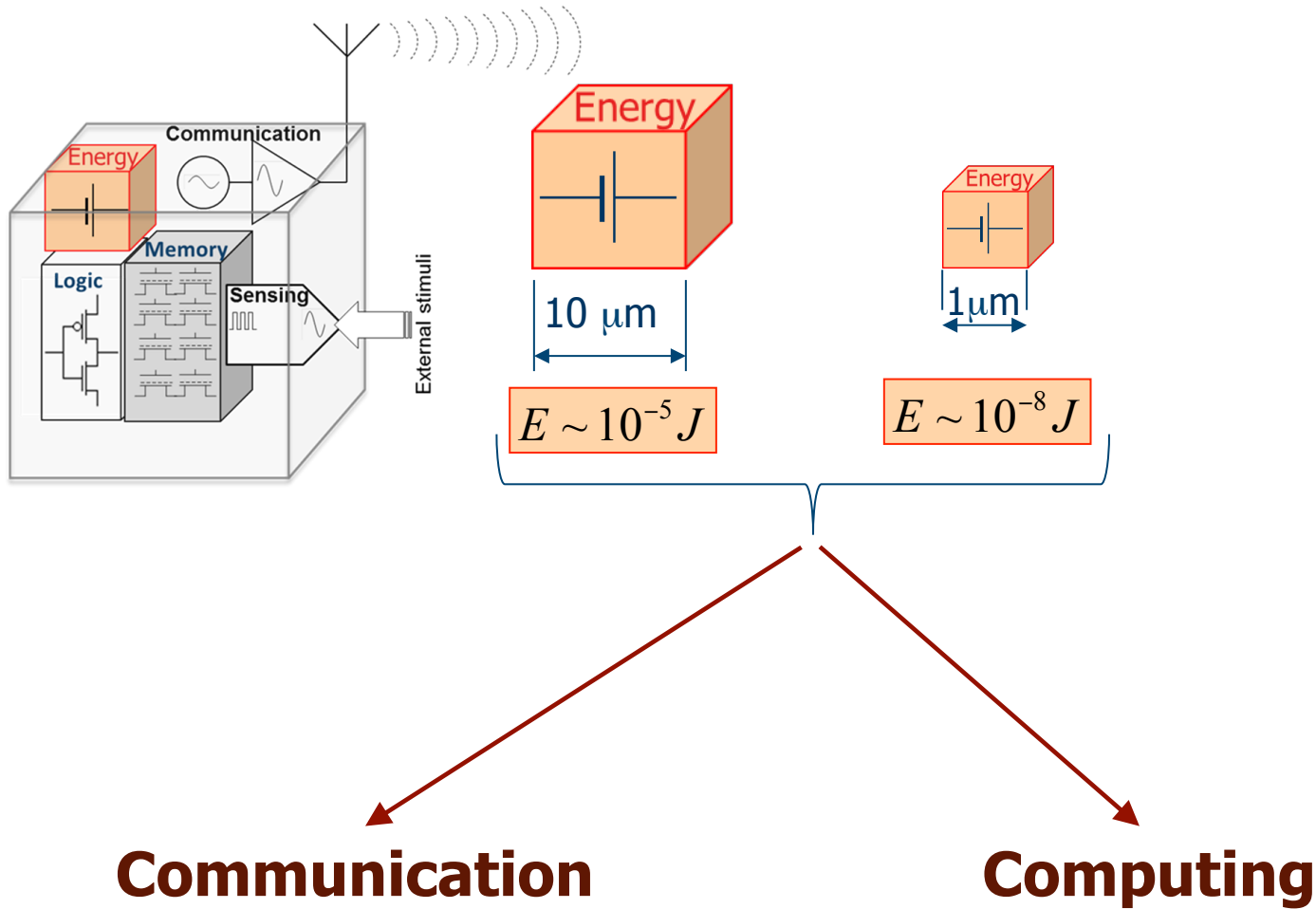
$$E_{\max} \sim eN_A \cdot 1V = 1.6 \times 10^{-19} \cdot 6 \cdot 10^{23} \sim 10^5 \frac{J}{\text{mole}} \sim 10^4 \frac{J}{\text{cm}^3}$$

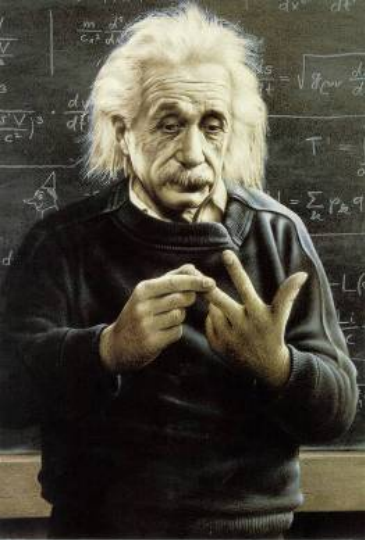
10 μm

$$E \sim (10^{-3} \text{cm})^3 \cdot 10^4 \sim 10^{-5} J$$

$$E \sim (10^{-4} \text{cm})^3 \cdot 10^4 \sim 10^{-8} J$$







Wireless Communication in the Small



Example: Uniformly radiated wireless communication

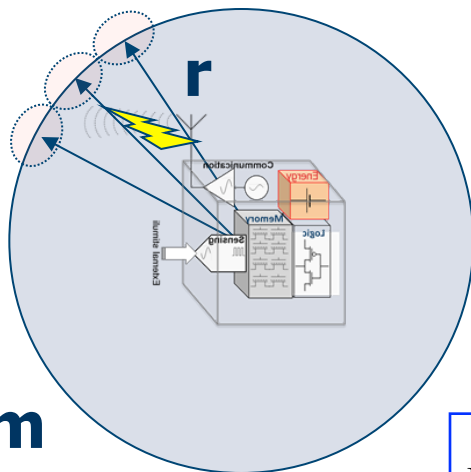
$$E_{\text{photon}} = h\nu = \frac{hc}{\lambda}$$

$$E_{\text{com}} = N_{\text{photons}} \cdot E_{\text{ph}}$$

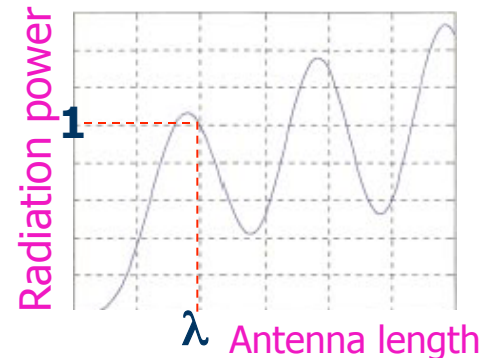
10 μm

$h = 6.63 \cdot 10^{-34} \text{ J}\cdot\text{s}$

$$N_{\text{photons}} \sim \frac{4\pi r^2}{\lambda^2}$$



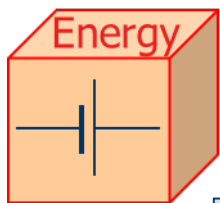
$$E_{\text{com}} \sim \frac{4\pi r^2 hc}{\lambda^3}$$



$\lambda_{\text{max}} \sim 10 \mu\text{m}$

Example: $r = 1\text{m}$

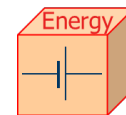
$$E_{\text{com}} = 4\pi \cdot 1^2 \cdot \frac{6.63 \cdot 10^{-34} \cdot 3 \cdot 10^8}{(10^{-5})^3} = 2.5 \cdot 10^{-9} \frac{\text{J}}{\text{bit}}$$



10 μm



$N_{\text{max}} = 4000 \text{ bit}$



1 μm

$E_{\text{com}} = 2.5 \times 10^{-6} \text{ J/bit}$

$E \sim 10^{-5} \text{ J}$

$E \sim 10^{-8} \text{ J}$

0 bit

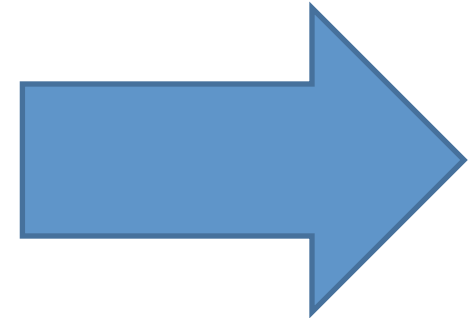
Communication energy/volume expenditures is most costly activity – should therefore maximize “system intelligence”



Layers of Intelligence

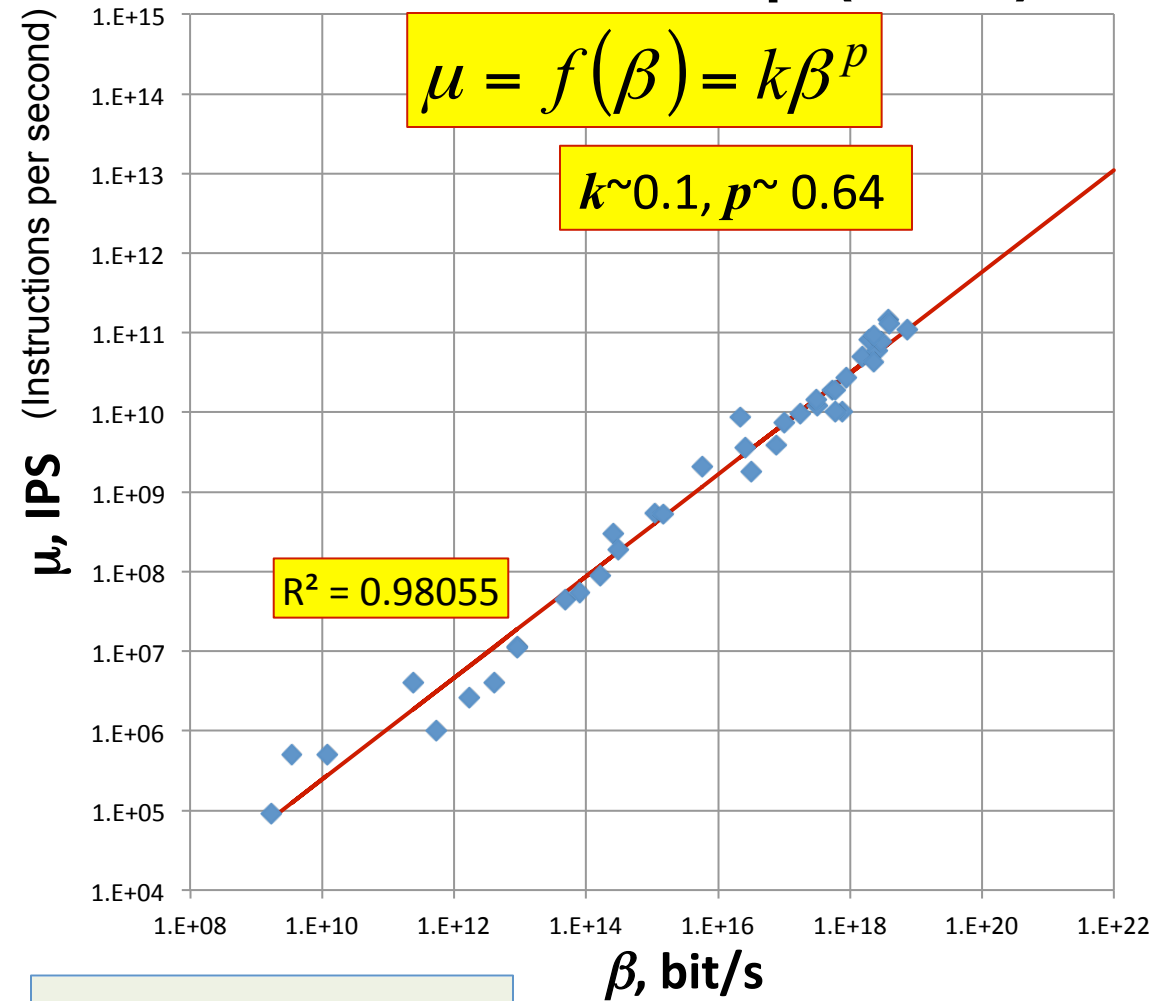
- 1) a. Number of binary elements (Logic and Memory)
b. Switching Speed

- 2) Binary Information Throughput (BIT), β
maximum number of binary transitions per
unit area per unit time
bits/s
a measure of computational capability on device level



- 3) Algorithmic Performance, μ
MIPS, MOPS, FLOPS...
a measure of computational capability on the processor level

Benchmark capability μ (IPS) as a function of β (bit/s)



$$\beta = N_{tr} \cdot f$$

a measure of computational
capability on device level

Company	Model	Year
Intel	4004	1971
Intel	8080	1974
MOS Technology	6502	1975
Motorola 68000	68000	1979
Intel	286	1982
Motorola	68020	1984
Intel	386DX	1985
ARM	ARM2	1986
Motorola	68030	1987
Motorola	68040	1990
DEC	Alpha 21064 EV4	1992
Intel	486DX	1992
Motorola	68060	1994
Intel	Pentium	1994
Intel	Pentium Pro	1996
IBM - Motorola	PowerPC 750	1997
Intel	Pentium III	1999
AMD	Athlon	2000
AMD	Athlon XP 2500+	2003
Intel	Pentium 4 Ext. Edition	2003
Centaur - VIA	VIA C7	2005
AMD	Athlon FX-57	2005
AMD	Athlon 64 3800+ X2	2005
IBM	Xbox360 "Xenon"	2005
Sony-Toshiba-IBM	PS3 Cell BE	2006
AMD	Athlon FX-60	2006
Intel	Core 2 Extreme X6800	2006
Intel	Core 2 Extreme QX6700	2006
P.A. Semi	PA6T-1682M	2007
Intel	Core 2 Extreme QX9770	2008
Intel	Core i7 920	2008
Intel	Atom N270	2008
AMD	E-350	2011
AMD	Phenom II X4 940	2009
AMD	Phenom II X6 1100T	2010
Intel	Core i7 980X	2010
Intel	Core i7 2600K	2011
Intel	Core i7 875K	2011
AMD	8150	2011

Turing-Heisenberg Rapprochement?



Number of binary elements

$$= \frac{n_{bit}}{t_{sw}}$$

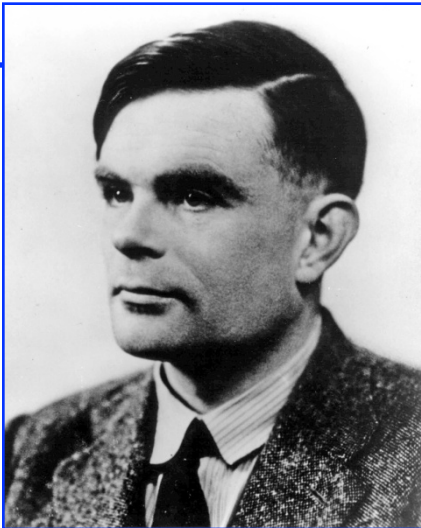
Switching time

Binary Information Throughput

a measure of computational capability on device level

Instructions per second
a measure of computational capability on the processor level

$$\mu = k \beta^p$$



Alan Turing

How can we increase MIPS?



Werner Heisenberg



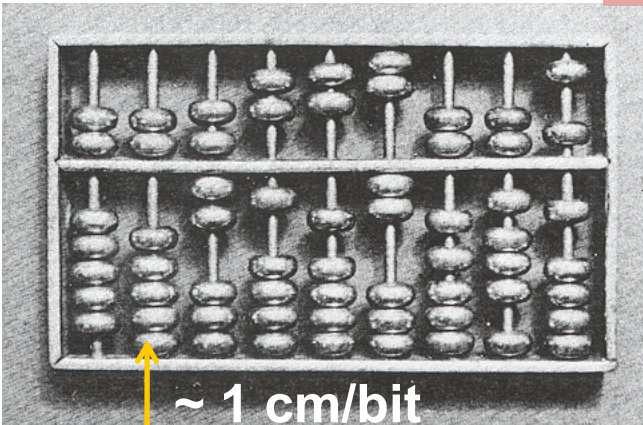
Ludwig Boltzmann

Can computational theory suggest new devices?
Stan Williams @ Nanomorphic Forum

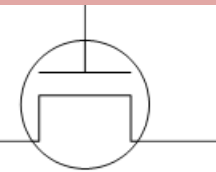
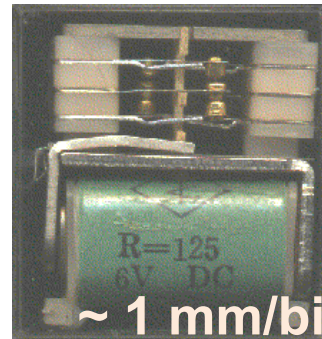
What is Information?

Information is measure of distinguishability

e.g. of a physical subsystem from its environment...



Information-bearing particles



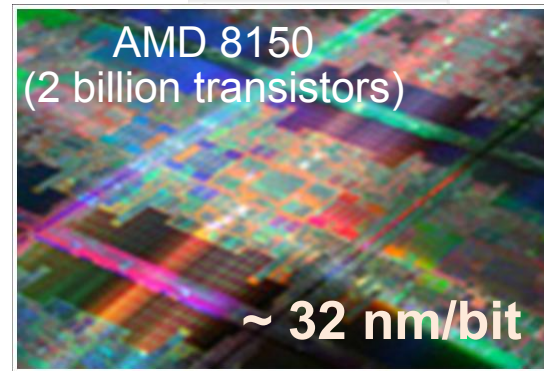
$$I = K \ln N$$

$$N_{\min} = 2$$

$$I(N_{\min}) = 1$$

$$1 = K \ln 2$$

$$K = \frac{1}{\ln 2}$$



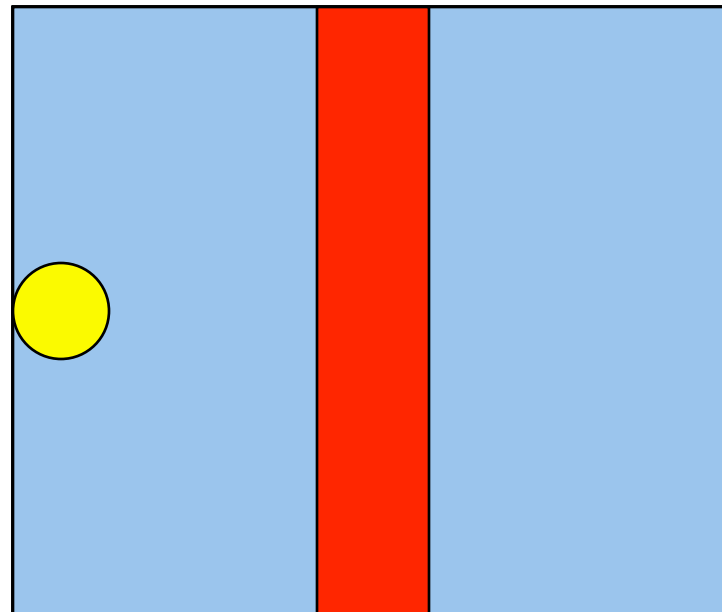
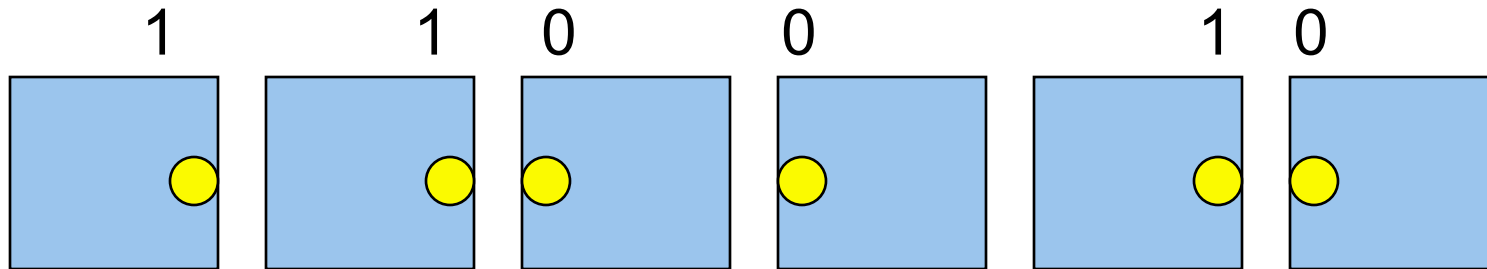
~ 0.5 nm/bit

A THEME: Minimal ICT Element

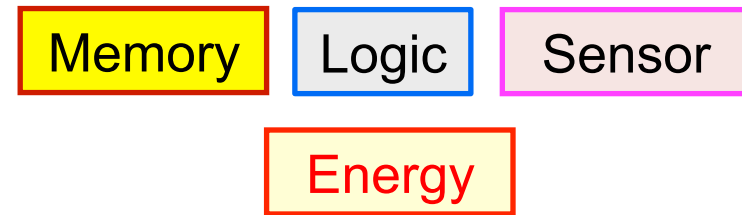
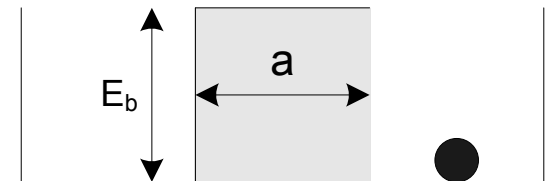
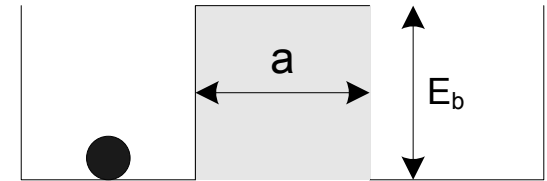
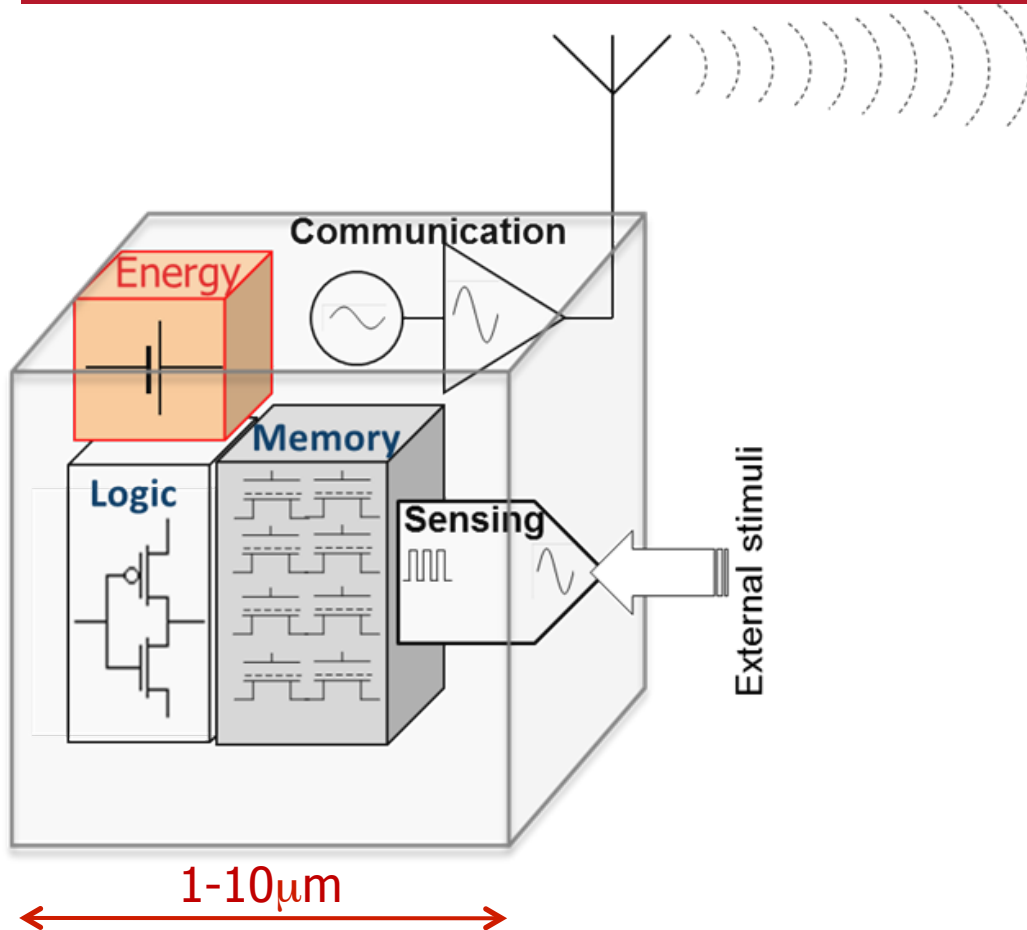
What is the smallest volume of matter needed for an ICT element? What is the smallest energy of operation?

Source: IBM

Particle Location is an Indicator of State



An abstract ICT-Energy element



Central Concept: **Energy Barrier**

How can a barrier be created and controlled in a physical system?

Lowest Barrier:

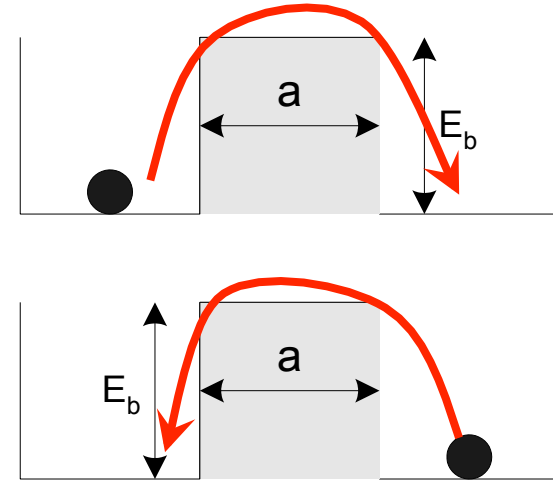
The Boltzmann constraint



Distinguishability D implies low probability Π of spontaneous transitions between two wells (error probability)

$$D=\max, \Pi=0$$

$$D=0, \Pi=0.5 \text{ (50\%)}$$



Classic distinguishability:

$$\Pi_{classic} = \exp\left(-\frac{E_b}{k_B T}\right)$$

Minimum distinguishable barrier: $\Pi=0.5$

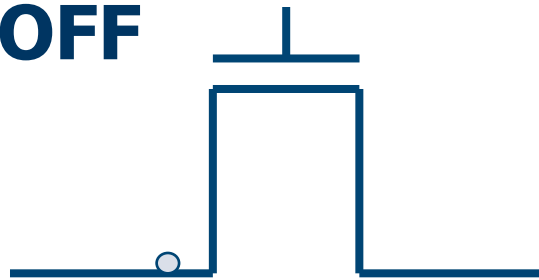
$$\frac{1}{2} = \exp\left(-\frac{E_b}{k_B T}\right) \longrightarrow E_b = k_B T \ln 2$$

Shannon - von Neumann - Landauer limit



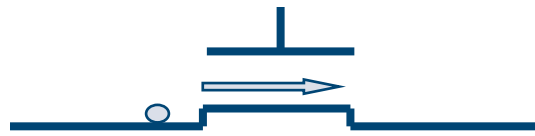
Switching Energy: Energy of Full-cycle

OFF



$$E_{OFF-ON} = E_b$$

ON



$$E_{carrier}$$

OFF



$$E_{ON-OFF} = E_b$$

$$E_{bit_{min}} = 2E_{b_{min}} + E_{carrier}$$

$$kT \ln 2$$

We are fighting ambient thermal energy!

$$E_{SW_{min}} = 3k_B T \ln 2$$

$$\times N$$

N – the number of electrons

$$E_{sw} = 2E_b + NE_w = (N+2)k_B T \ln 2$$

Scaling Limits: The Heisenberg Constraint



$$E_b = k_B T \ln 2$$

Electrons in semiconductors: $m^* = 0.15 - 0.20 m_0$

$$\Delta p = \sqrt{2mE_b}$$

$$\Delta x \Delta p \geq \hbar$$

$$\Delta E \Delta t \geq \hbar$$



At this size, tunneling will destroy the state

$$a_{crit} \sim \frac{\hbar}{\sqrt{2mE_b}} \quad \sim 3-4 \text{ nm}$$

$$t_{min} \sim \frac{\hbar}{E_b} \quad \sim 40 \text{ fs}$$



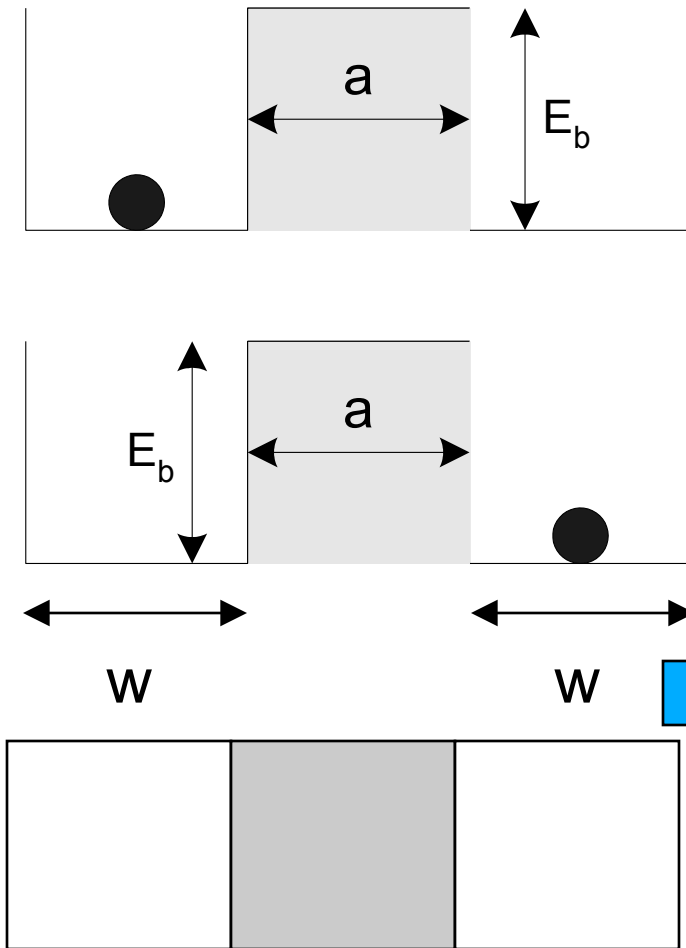
WRITE

Minimal time of dynamical evolution of a physical system
 N. Margolus and L. B. Levitin, Physica D 120 (1998) 188

Two-well bit – Maximum areal density



Joyner tiling



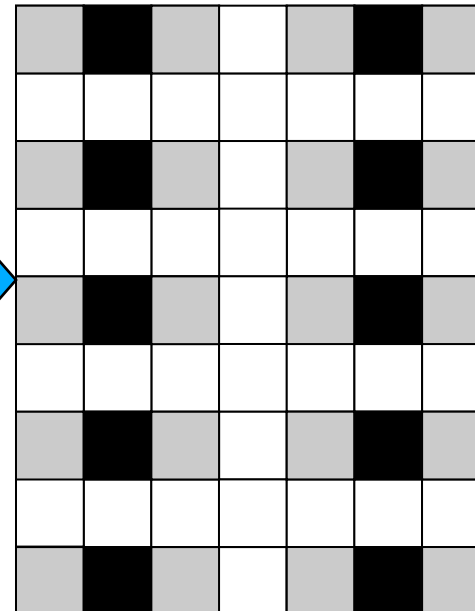
Device density

1) Upper Bound

$$n_{\max} = \frac{1}{8a^2}$$

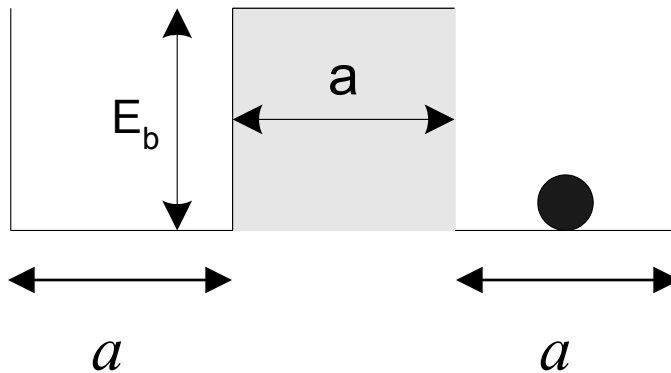
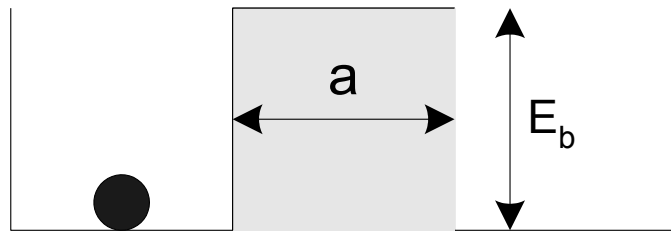
2) IC (ITRS)

$$n_{MPU} = \frac{1}{(20a)^2}$$

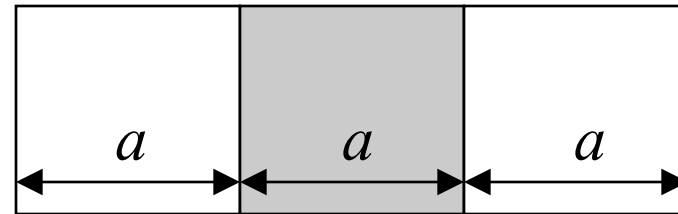


Generic Floorplan of a binary switch

Binary switch abstraction: Generic floorplan and energetics



Generic Floorplan of a binary switch



$$a = \frac{h}{\sqrt{2mkT \ln 2}} \sim 3 - 4 \text{ nm}$$

Practical limit ~5nm

$$Area_{\min} = 3a^2$$

$$E_{sw_{\min}} = 3k_B T$$

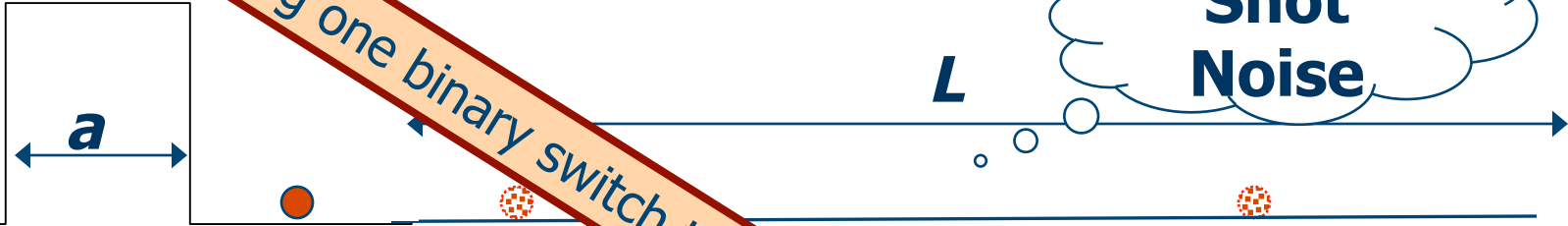
$$\varepsilon = k_B T \left(\frac{J}{\text{tile}} \right)$$

$\Pi_{\text{error}} = 0.5$



Connecting Binary Switches via Wires: *Extended Well Model*

The problem is to 'place' the electron on the down stream gate – more than one electron is needed to 'charge' the line



A

B

$$\Pi_{CD} = \frac{a}{L}$$

C

D

Example: $L=4a$
 $N=1 \rightarrow P < 0.25$

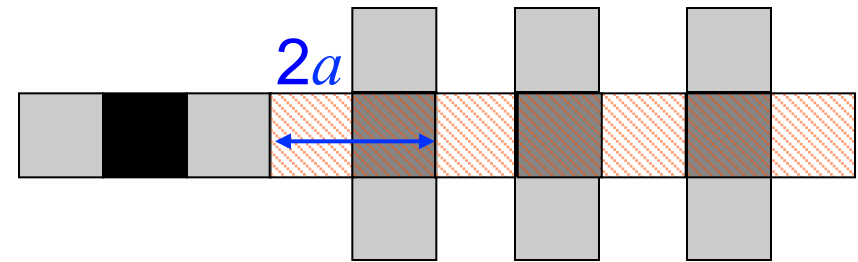
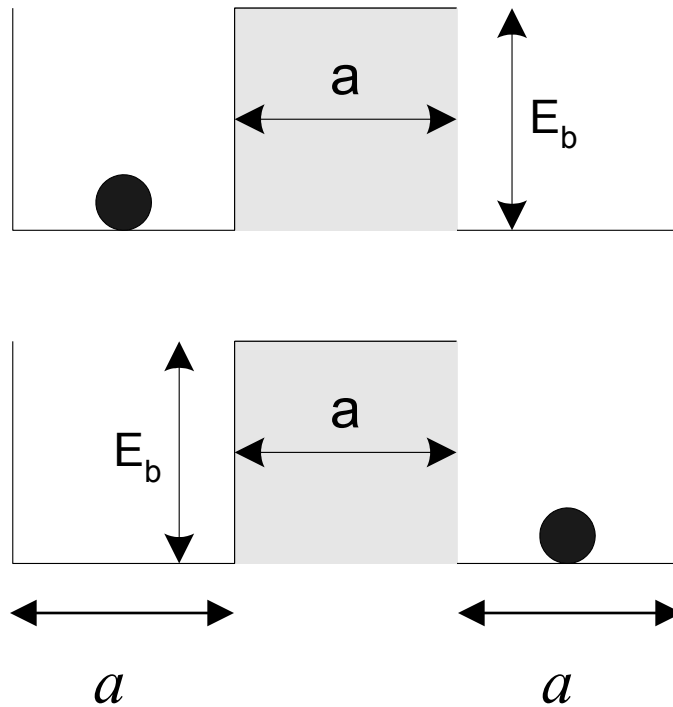
In General:

$$\Pi = 1 - \left(1 - \frac{a}{L}\right)^N$$

N – the number of electrons

Note: Connecting one binary switch to another one doesn't yet do computation!

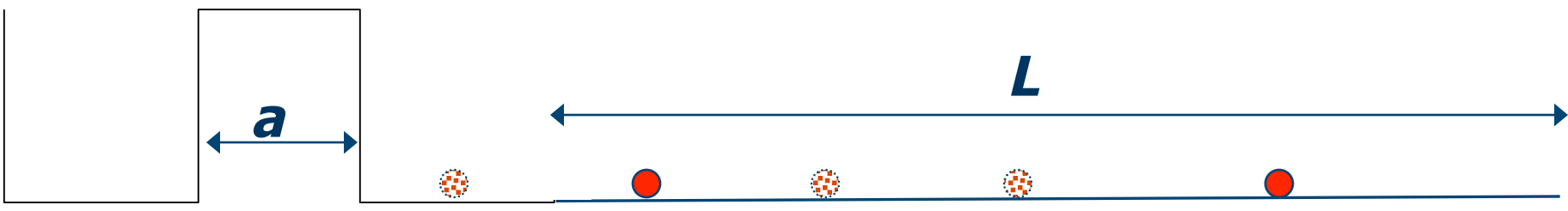
Interconnect abstraction: *Extended Well Model*



$$L_{\min} = 2a \cdot F$$

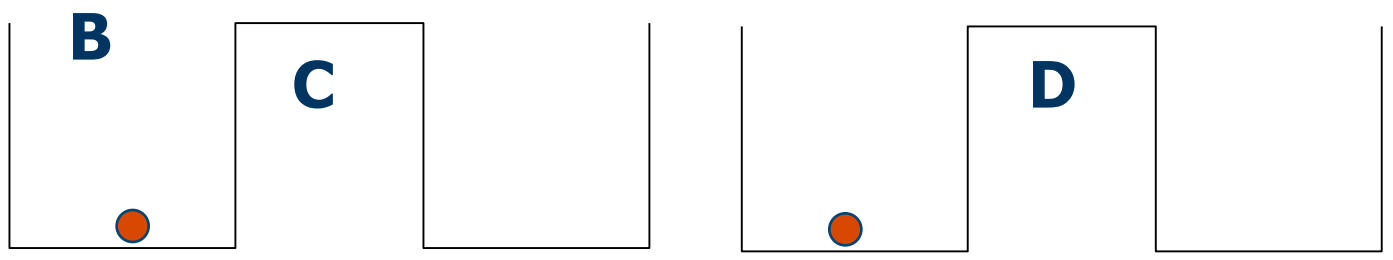
SRG[®] Connecting Binary Switches via Wires in 2D ($L > 2na$, N electrons)

For logic operation, a binary switch needs to control at least two other binary switches



A

Shot Noise



$L > 2na$

n - fan

N – the number of electrons

$n=2$
 $L=4a$

$N_{min}=5$

N	Π
1	0.06
2	0.19
3	0.33
4	0.47
5	0.58
6	0.68

$$\Pi_{C\&D} = \Pi_C \times \Pi_D = \left(1 - \left(1 - \frac{a}{L} \right)^N \right)^2$$

SRG Minimum switching energy for connected binary switches

$$E_{sw} = 2E_b + NE_b = (N+2)E_b$$

F02

F04

$n=2$
 $L=4a$

$n=4$
 $L=8a$

$N_{min}=5$

$N_{min}=14$

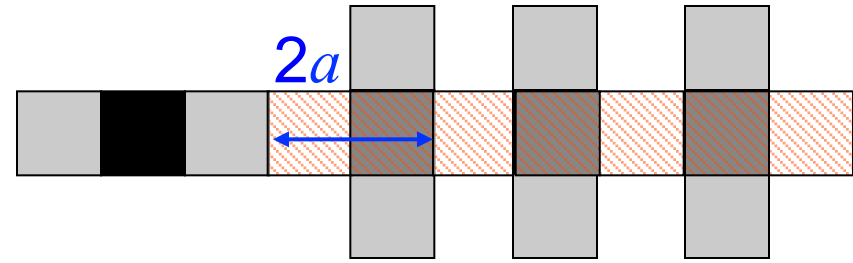
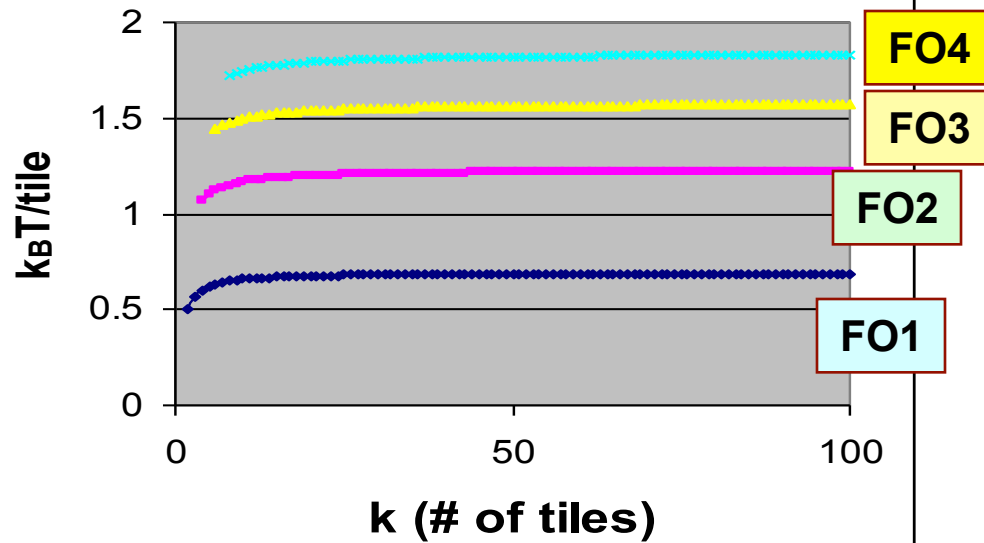
$E_{sw} = 7k_B T \ln 2$

$E_{sw} = 16k_B T \ln 2$

Communication between logic switches takes more energy than information processing (switch operations)

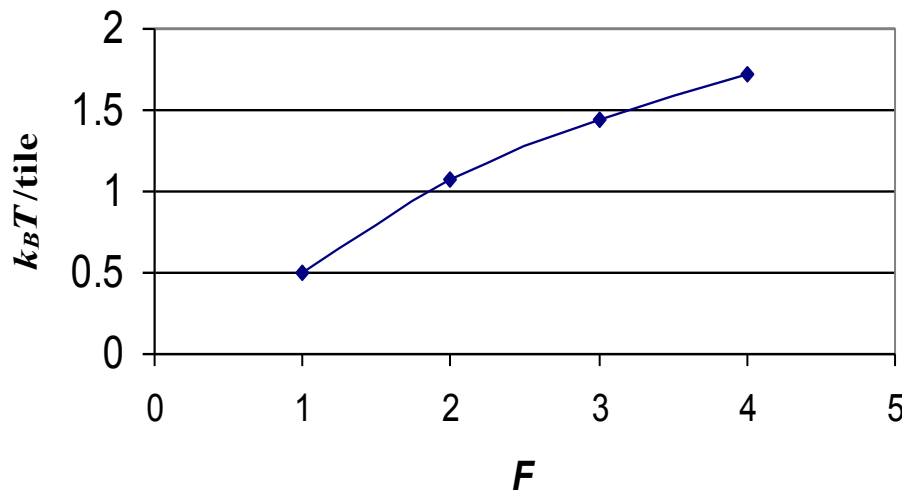
N	Π
1	0.00
2	0.00
3	0.01
4	0.03
5	0.06
6	0.09
7	0.14
8	0.19
9	0.24
10	0.29
11	0.35
12	0.41
13	0.46
14	0.51
15	0.56
16	0.60
17	0.65
18	0.68

In the limits: Energy per interconnect tile



Long interconnect limit

$$\langle \varepsilon \rangle = 1.33 \frac{k_B T}{\text{tile}}$$



Minimum interconnect limit

$$\langle \varepsilon \rangle = 1.18 \frac{k_B T}{\text{tile}}$$

$\Pi=0.5$

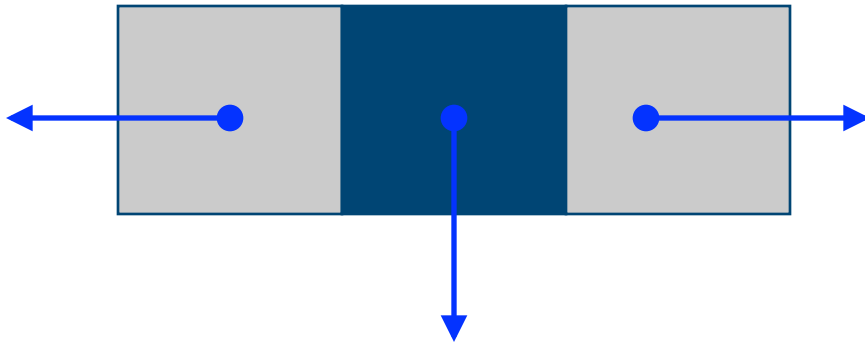
$$\varepsilon \sim k_B T / \text{tile}$$



Floorspace Expenses of Communication between Binary Switches

Assumption: For each of 3 tiles of Binary Switch we need at least:

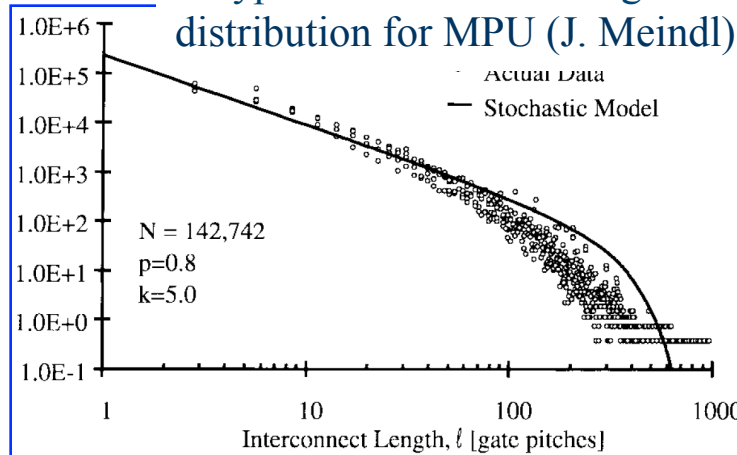
One contacting interconnect tile (3 total) and one connecting interconnect tile (3 total)



Total 6 interconnect tiles per binary switch

$$L_{int} \sim 6a$$

A typical interconnect length distribution for MPU (J. Meindl)



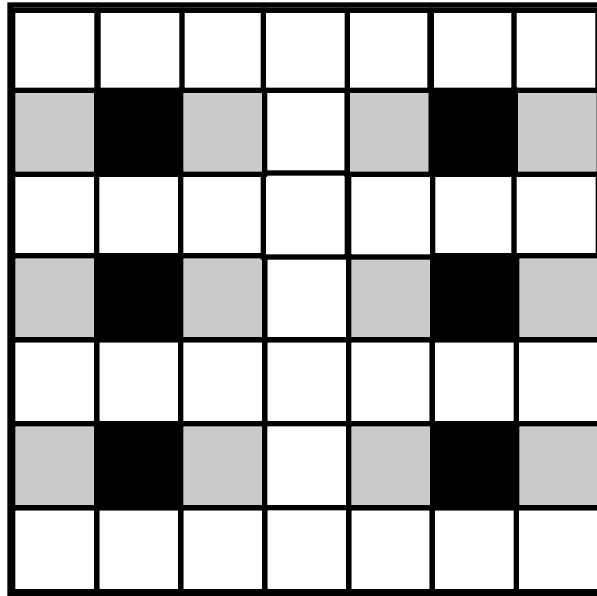
n, cm^{-2}	$\bar{L}(n)/L_g$
1.E+02	4.1
1.E+04	6.4
1.E+06	8.3
1.E+08	9.7
1.E+10	10.5

Reality check:

Digital circuit abstraction: Generic floorplan and energetics and speed



Switching energy of one binary switch in a circuit



3 switch tiles

$$E_{sw} = 3E_b + 6E_b = 9k_B T \ln 2$$

6 wire tiles

Operational energy of a circuit of
 n binary switches:

(50% activity)

$$E_{op} = \frac{9}{2} n k_B T \ln 2$$

$$Area_{min} = n \cdot 8a^2 \quad \text{Joyner tiling}$$

Switching delay of one binary switch in a circuit:

Speed: $\tau_{min}/tile$

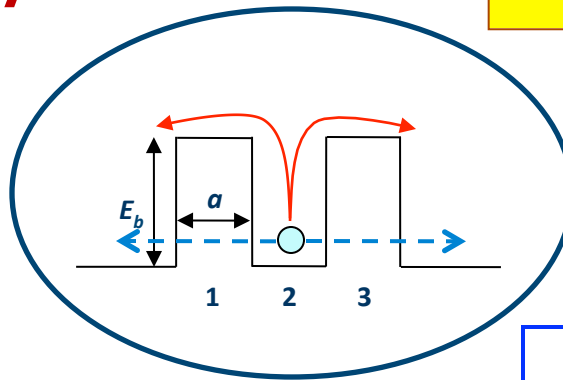
$$\tau_{min} = \frac{\hbar}{kT \ln 2} \quad \sim 40 \text{ fs}$$

$$t_{sw} = 9 \tau_{min}$$

What is the smallest volume of matter needed for memory?

$$t_s = \frac{e}{I_s} \sim 10y$$

$$I_{o-b} = \frac{e}{h} \cdot k_B T \cdot \exp\left(-\frac{E_b}{k_B T}\right)$$



$$t_{o-b} = \frac{h}{k_B T} \exp\left(\frac{E_b}{k_B T}\right)$$

$$I_T = \frac{e}{h} \cdot k_B T \cdot \exp\left(-\frac{2\sqrt{2m}}{\hbar} \cdot a \cdot \sqrt{E_b}\right)$$

$$E_{b\min} = k_B T \ln\left(\frac{k_B T}{h} t_s\right)$$

$$a_{\min} = \frac{\hbar}{2\sqrt{2mE_b}} \ln\left(\frac{k_B T}{h} t_r\right)$$

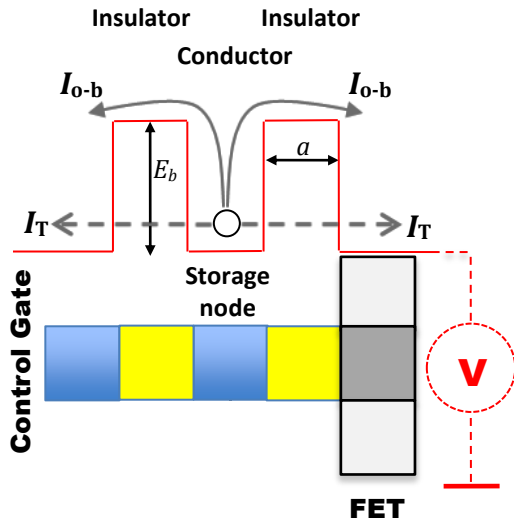
$$E_{b\min} = 1.3 \text{ eV}$$

$$a_{\min} = 4.30 \text{ nm}$$

(Limited by the mass of electron)

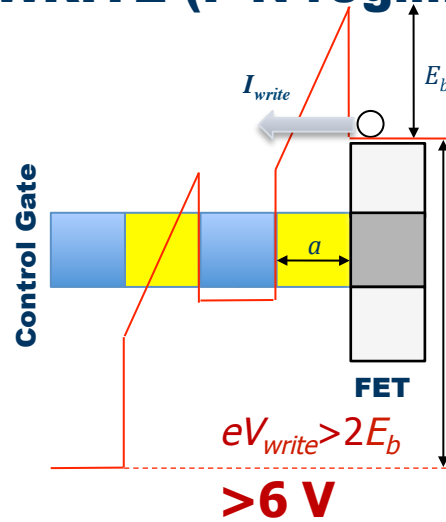
Adjustments: effective mass, electrostatics etc.: $a_{\min} \sim 5 \text{ nm}$, $E_{\min} \sim 2-3 \text{ eV}$

1. Basic Concept



$E_{bmin} > 1.7 \text{ eV}$ (>10 y retention)
 $E_{b \text{ SiO}_2} = 3.1 \text{ eV}$
 $a_{min} \sim 5 \text{ nm}$

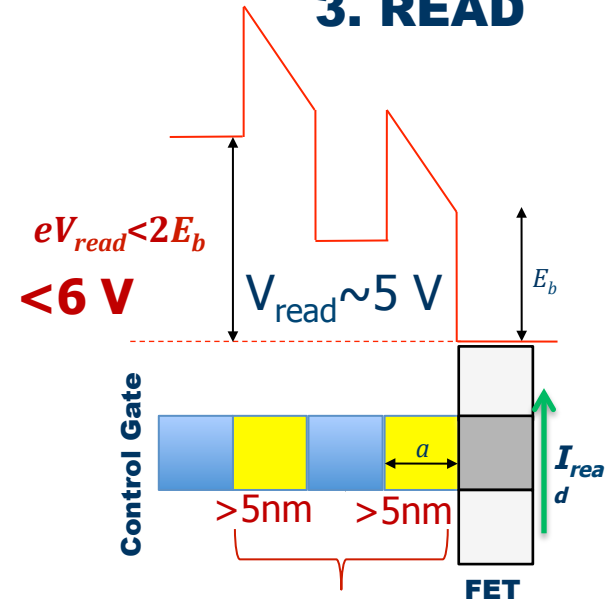
2. WRITE (F-N regime)



$V_{write \text{ min}} > 6\text{-}7 \text{ Volt}$ (very slow)

$V_{write} > 10\text{-}15 \text{ Volt}$ (ms- μ s)

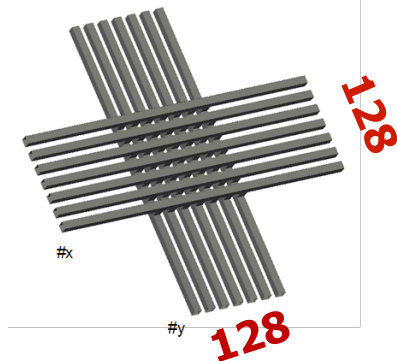
3. READ



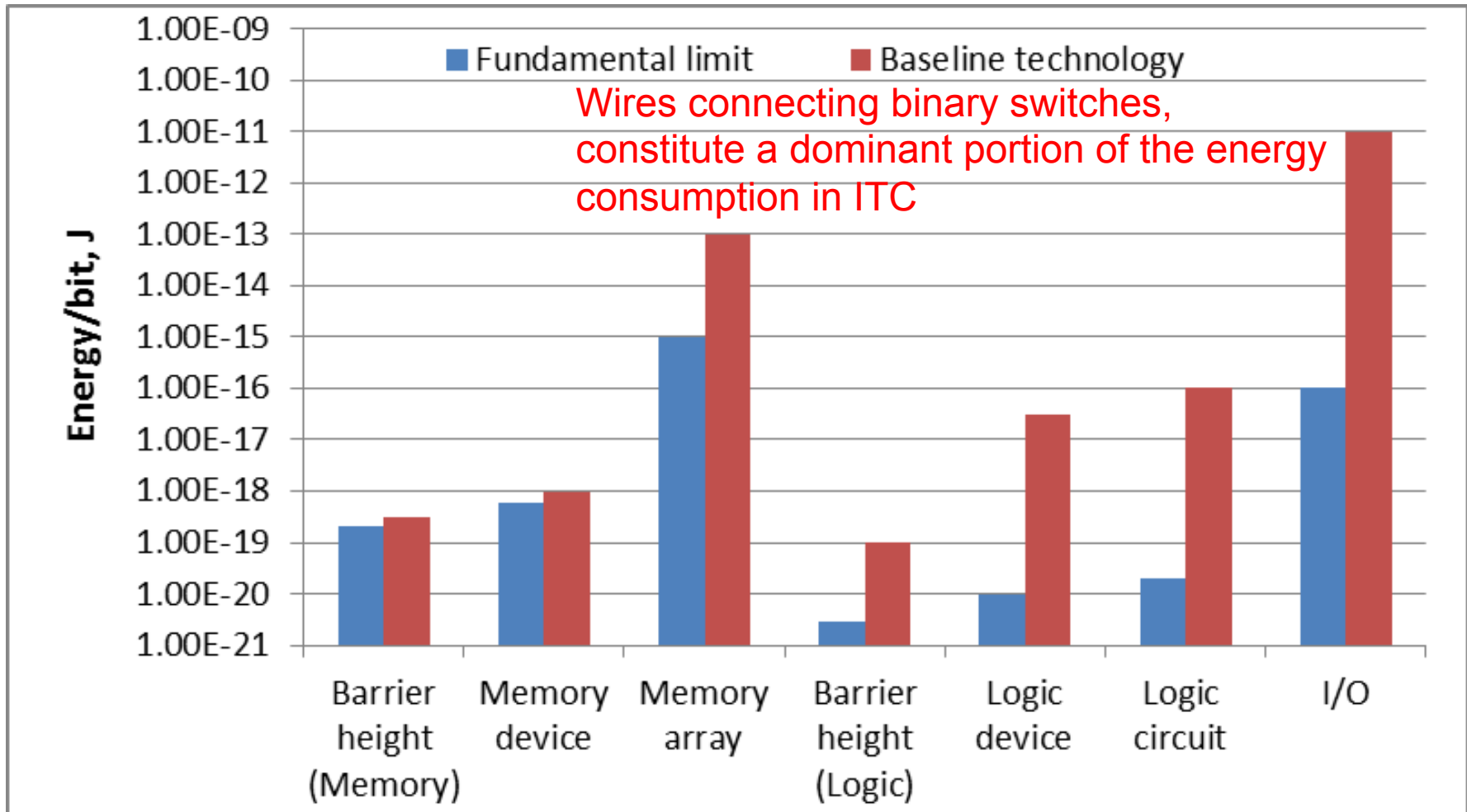
$$\frac{T_{ox}}{L_{ch}} \sim 1$$

$F_{min} > 10\text{nm}$

4. Array

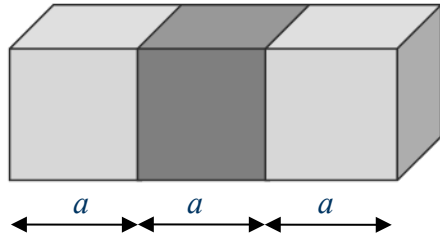


$$E_M \sim C_{line} V^2 \sim 10^{-14} \text{ J}$$



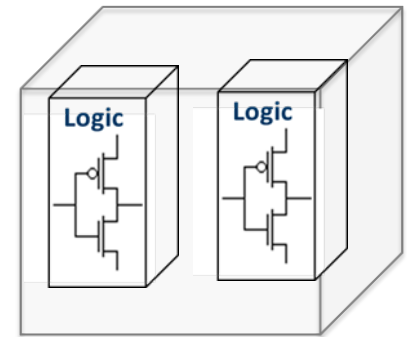
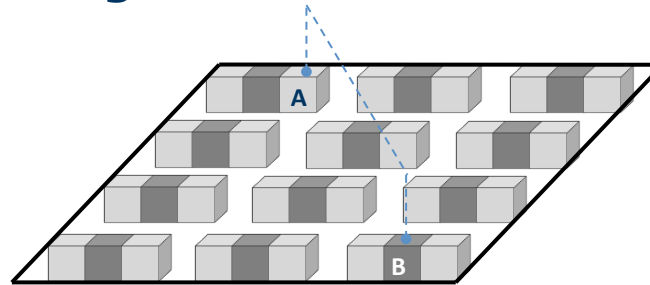
Minimal 3D Electronic Logic Switch: Volume bounds

3D tiling



$a_{\min} \sim 5 \text{ nm}$

(Limited by the mass of electron)

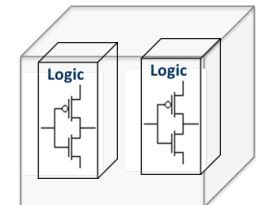


$$N_{tr} = 8 \times 10^7$$

10 μm

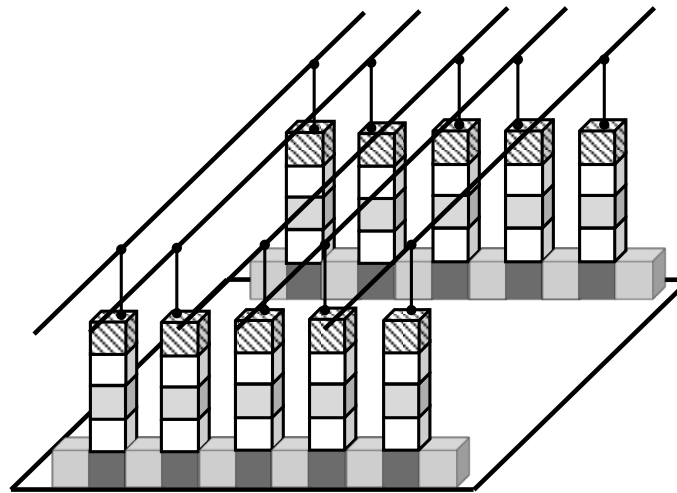
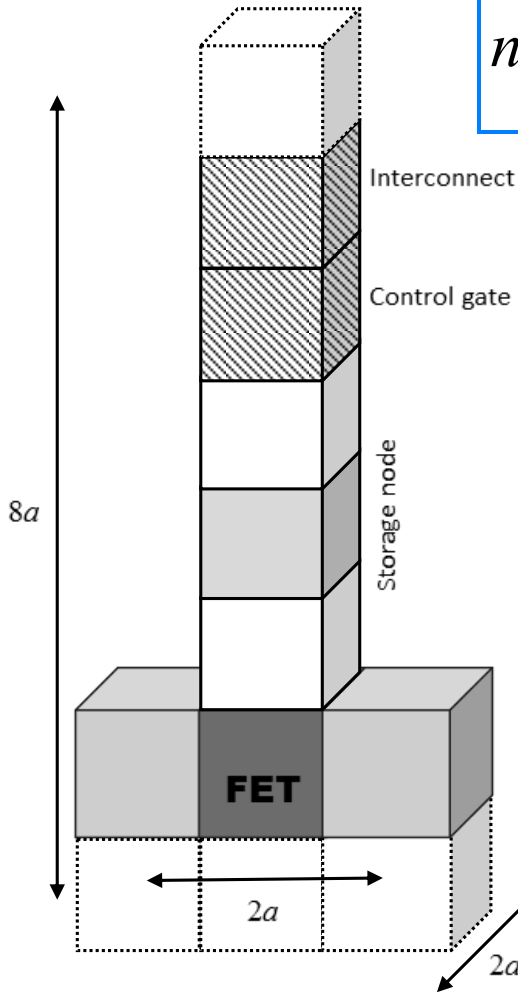
$$n_{3D} \sim \frac{1}{96a^3} \sim 8 \cdot 10^{16} \frac{\text{bit}}{\text{cm}^3}$$

$$N_{tr} = 8 \times 10^4$$



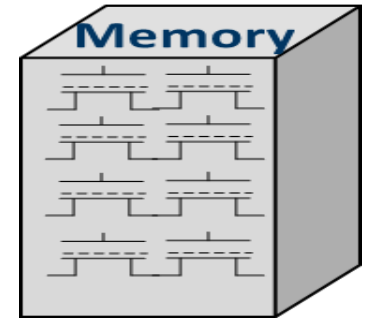
1 μm

$$n_{3D} \sim \frac{1}{32a^3} \sim 10^{17} \frac{\text{bit}}{\text{cm}^3}$$



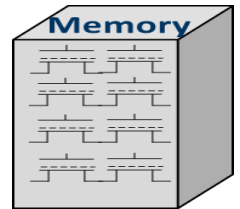
$a_{\min} \sim 5 \text{ nm}$

(Limited by the mass of electron)



10 μm

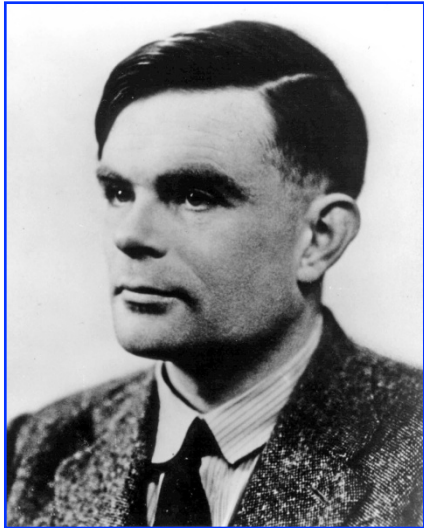
$N \sim 100 \text{ Mbit}$



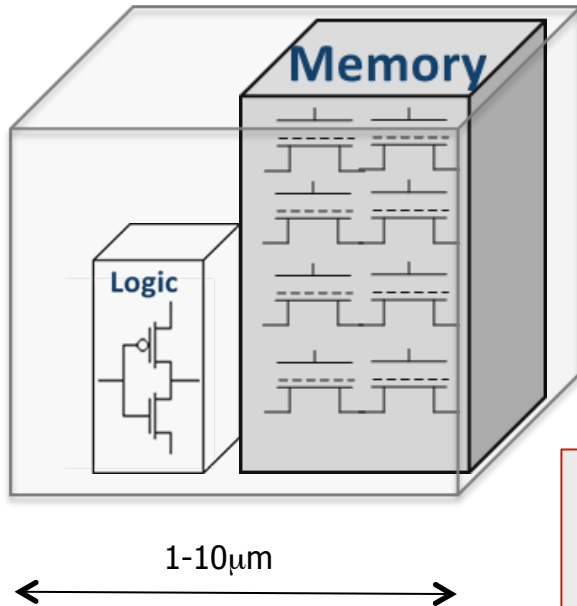
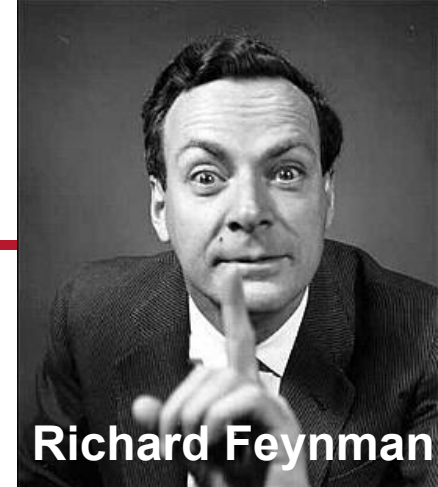
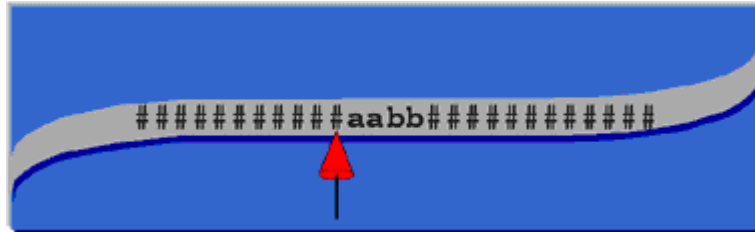
1 μm

$N \sim 100 \text{ kbit}$

Miniaturizing Limits of a Computer?

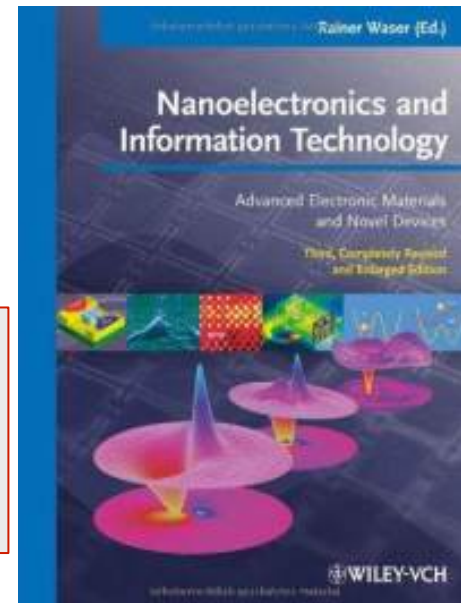


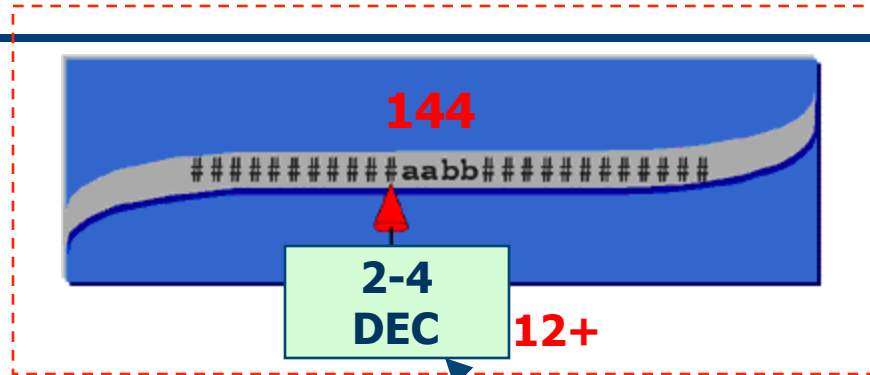
Turing Machine



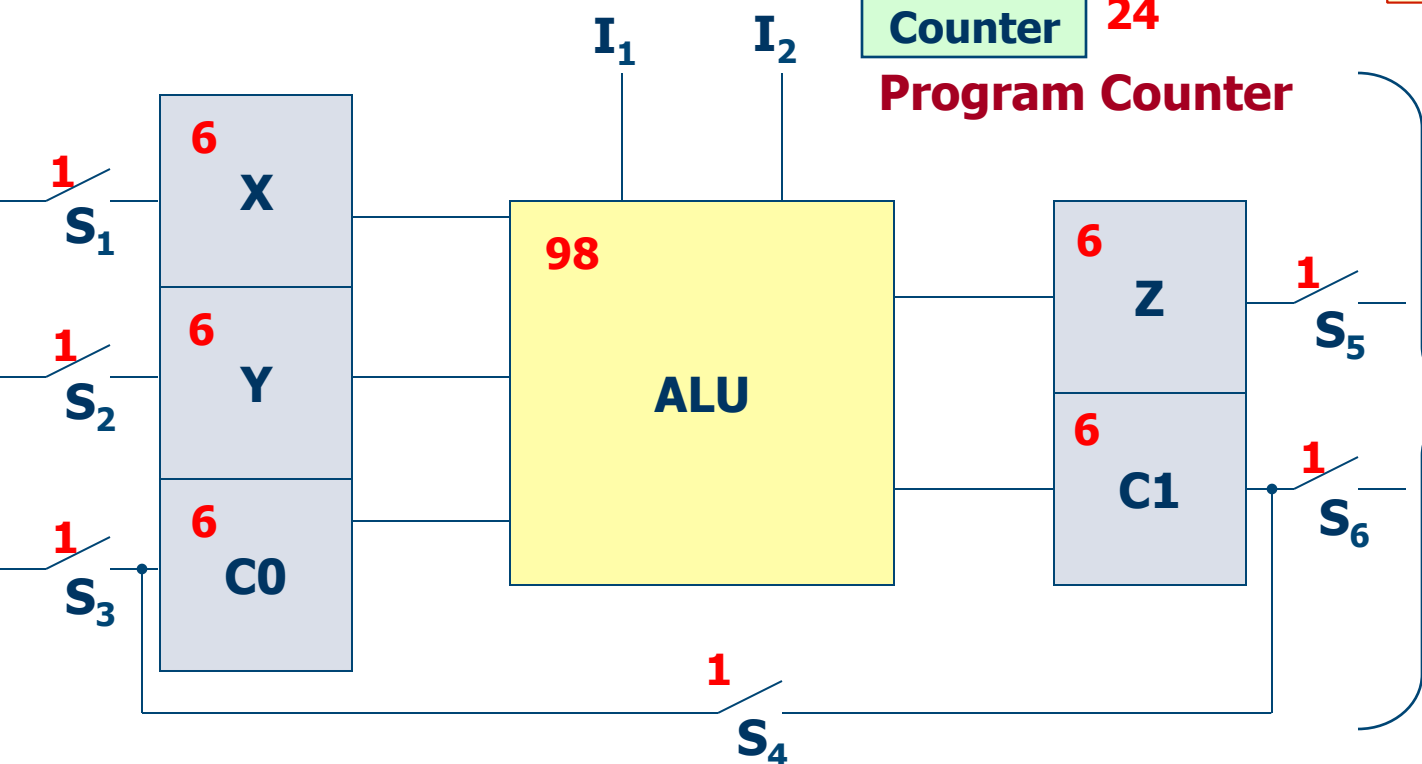
A complete 'computer' must contain both logic unit and 'tape' (nonvolatile memory)

R. Cavin, W. Joyner, and T. Noll, **Chapter 22:** *Performance Estimates for Microprocessors: at Technology Limits and in Practice*, in: **Nanoelectronics and Information Technology**, by R. Waser (Ed.) (Wiley 2012)





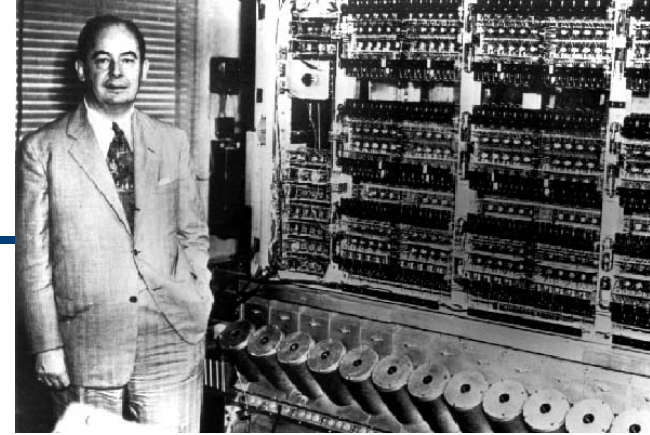
~500 "raw" bit transitions per useful bit



Total: 320 devices



Von Neumann's Threshold



John von Neumann:

If one constructs the automaton (A) correctly, then any additional requirements about the automaton can be handled by sufficiently elaborated instructions. This is only true if A is sufficiently complicated, if it has reached a certain minimum of complexity

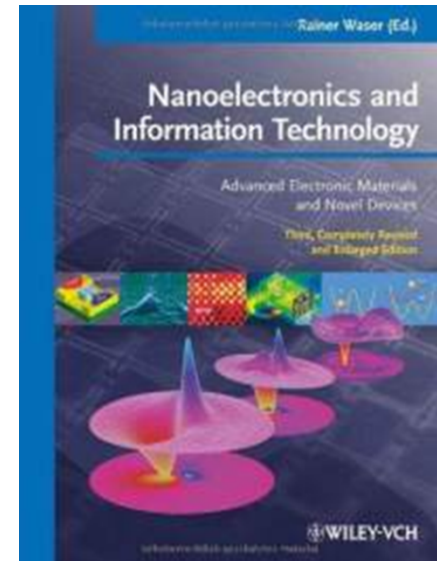
Von Neumann's estimate: $N_{min} \sim$ a few hundred switches
(J. von Neumann, *The Computer and the Brain*. Yale Univ. Press, 1959)

Cavin-Joyner-Noll abstraction (CJN):

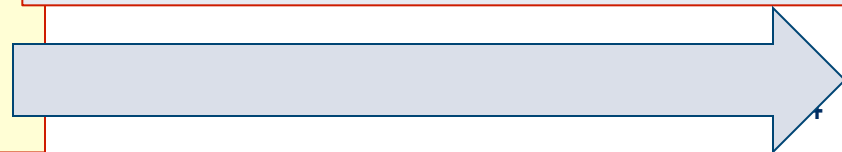
In an attempt for a more accurate estimate of the von Neumann threshold, a model 1-bit Minimal Turing Machine (MTM) has been constructed

MTM Essentials:

Total device count:	320
Instruction word length:	8-bit
Cycles per output bit:	3
"Raw" bits processed per output bit:	~500



R. Cavin, W. Joyner, and T. Noll, **Chapter 22: Performance Estimates for Microprocessors: at Technology Limits and in Practice**, in: **Nanoelectronics and Information Technology**, by R. Waser (Ed.) (Wiley 2012)



Si- μ Cell: A hypothetical $1\mu\text{m}^3$ Si computer

Logic

$$N_{tr} = 320,$$

$$E_b = 6k_B T \quad (\Pi_{\text{syst}} = 0.5)$$

$$E_{sw} = 54k_B T$$

$$E_{\text{cycle}} = 8640k_B T = 3.6 \times 10^{-17} \text{ J/cycle}$$

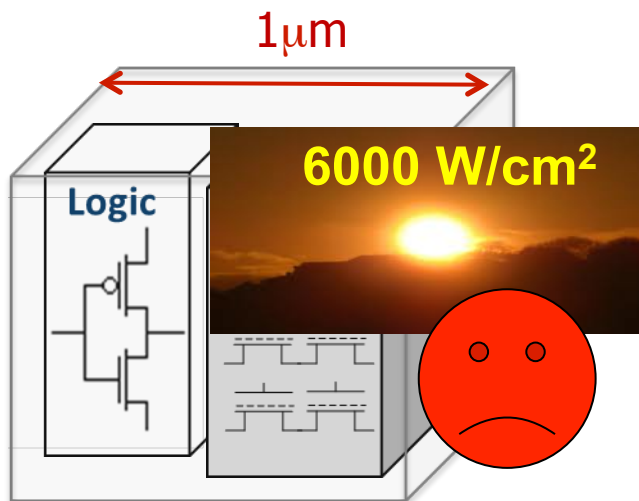
$$t_{\text{cycle}} \sim 16 \text{ ps}$$

$$P = \frac{E_L + E_M}{t_{\text{cycle}}} \sim \frac{3.6 \cdot 10^{-17} + 10^{-14} \text{ J}}{16 \text{ ps}} = 6.27 \cdot 10^{-4} \text{ W} = 627 \mu\text{W}$$

Memory

$$N = 100 \text{ kbit}$$

$$E_M \sim 10^{-14} \text{ J}$$



$$\frac{P}{A_{1\mu\text{m}}} = \frac{627 \mu\text{W}}{6 \cdot (1\mu\text{m})^2} = 10540 \frac{\text{W}}{\text{cm}^2}$$

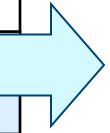
Must slow down!

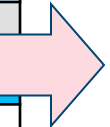
Exceeds capability of known cooling techniques



Heat-constrained operation

	Heat transfer coefficient, $W/(cm^2 \cdot K)$	Heat flux, $W/(cm^2)$
<i>Cooling techniques</i>		
Free convection, air	$(5-25) \times 10^{-4}$	0.05-0.25 ($\Delta T=100K$)
Free convection, water	$(20-100) \times 10^{-4}$	0.2-1 ($\Delta T=100K$)
Forced convection, air	$(10-500) \times 10^{-4}$	0.1-5 ($\Delta T=100K$)
Forced convection, water	$(100-15,000) \times 10^{-4}$	1-150 ($\Delta T=100K$)
<i>Reference examples</i>		
Human body	—	0.01
Hot plate	—	10
Microprocessor chip	—	20-60
Sun's surface	—	6000

 No overheads

 Space and energy overheads

If it is postulated that only passive cooling can be used for the *Si- μ Cell*, the maximum heat flux through the walls of the cube must be **<1W/cm²**.

total power **<6 \times 10⁻⁸ W**
cycle time **>170ns.**

Si- μ Cell: A hypothetical $1\mu\text{m}^3$ Si computer

Logic

$$N_{tr} = 320,$$

$$E_b = 6k_B T \quad (\Pi_{\text{syst}} = 0.5)$$

$$E_{sw} = 54k_B T$$

$$E_{\text{cycle}} = 8640k_B T = 3.6 \times 10^{-17} \text{ J/cycle}$$

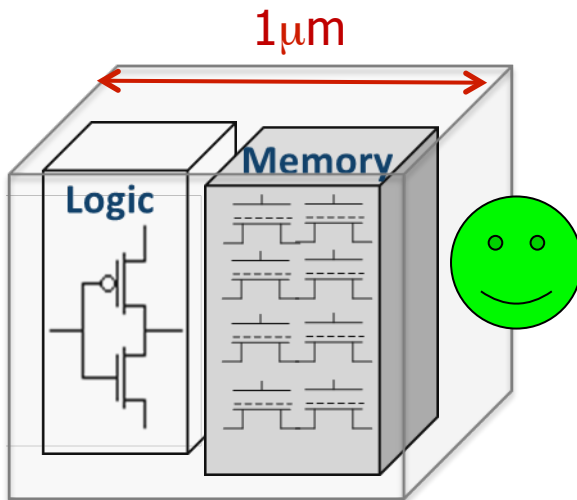
$$t_{\text{cycle}} \sim 170\text{ns}$$

Memory

$$N = 100 \text{ kbit}$$

$$E_M \sim 10^{-14} \text{ J}$$

$$P = \frac{E_L + E_M}{t_{\text{cycle}}} \sim \frac{3.6 \cdot 10^{-17} + 10^{-14} \text{ J}}{170\text{ns}} = 6 \cdot 10^{-8} \text{ W} = 60\text{nW}$$



$$\frac{P}{A_{1\mu\text{m}}} = \frac{60\text{nW}}{6 \cdot (1\mu\text{m})^2} = 1 \frac{\text{W}}{\text{cm}^2}$$

System's "intelligence" per a volume of matter

Si- μ Cell: A hypothetical $1\mu\text{m}^3$ Si computer



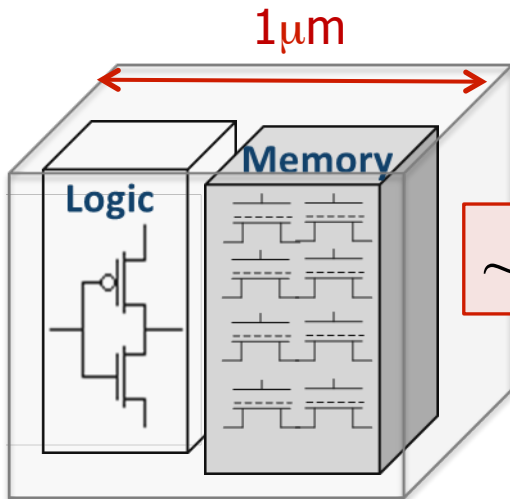
$$a_{min} \sim 5 \text{ nm}$$

Logic

$$n_{3D} \sim 8 \cdot 10^{16} \frac{\text{bit}}{\text{cm}^3}$$

Memory

$$n_{3D} \sim 2.5 \cdot 10^{17} \frac{\text{bit}}{\text{cm}^3}$$



$$\sim 10^{11} \text{ MIPS/cm}^3$$

Binary Information Throughput

$$N_{tr} = 320,$$

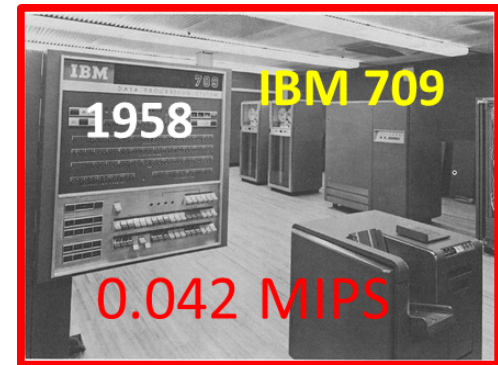
$$t_{cycle} \sim 170 \text{ ns}$$

$$\beta \sim 2 \times 10^9 \text{ bit/s}$$

$$\mu = k\beta^p$$

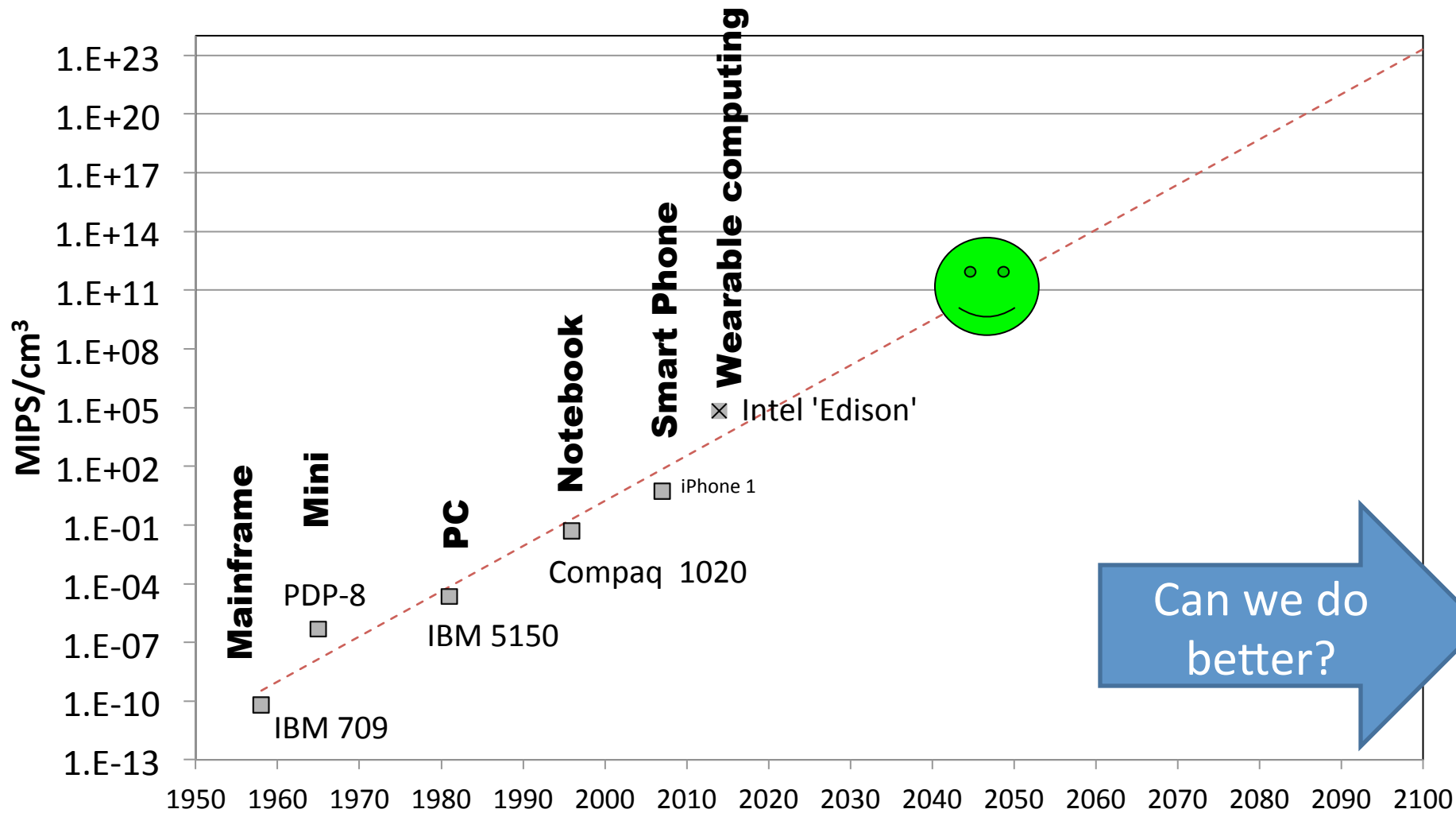
Algorithmic performance

$$\mu \sim 0.15 \text{ MIPS}$$



System's "intelligence" limit
for electron based systems?





How can we go below 5 nm?

$$\mu = k\beta^p$$

$$= \frac{n_{bit}}{t_{sw}}$$

Devices having feature sizes less than 5 nm should utilize particles whose mass is greater than the mass of an electron. Below about 5 nm, the mass of information-bearing particle should exceed free electron mass.

$$L_{\min} = \frac{\hbar}{\sqrt{2mE_b}}$$

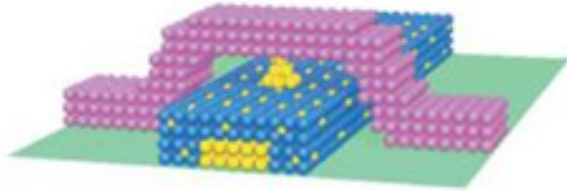
**Moving atoms instead
of moving electrons?**



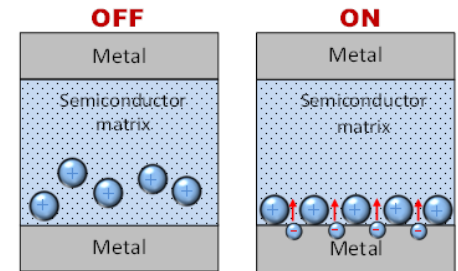
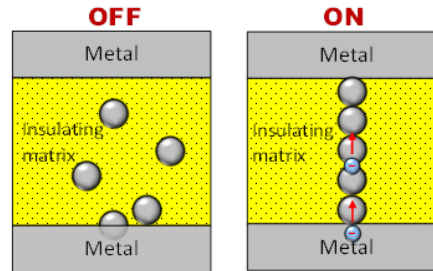
*This conclusion resulted
from the Heisenberg limit
on device size*

Moving Atoms: Nanoionics

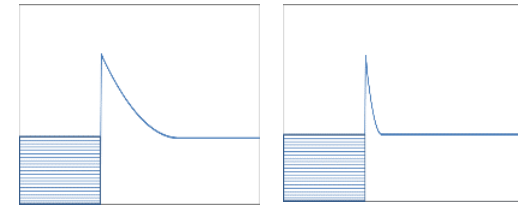
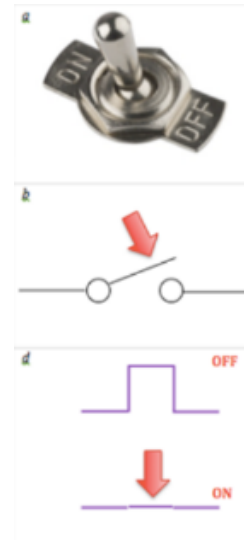
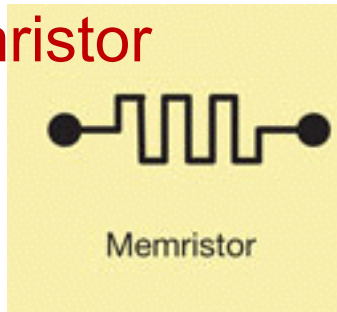
Atomic switch



Terabe et al., *Nature* 433, 47-50 (2005)

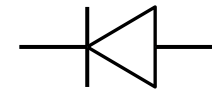


Memristor

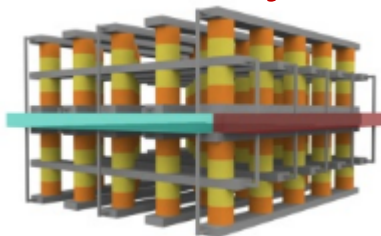


OFF

ON



Resistive memory



Lee et al. *Nature Mater.* 10, 625–630 (2011)

Feature size

Demonstrated 9 nm

Switching time

Demonstrated 0.3ns

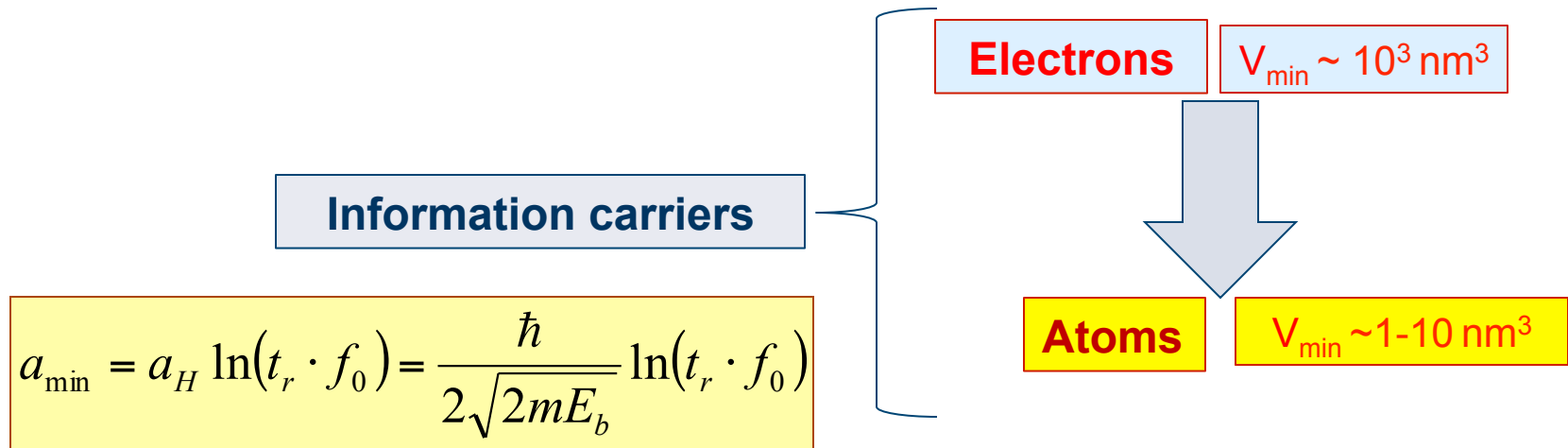


A SUMMARY:

Minimal solid-state binary element



What is the smallest volume of matter needed for a memory cell?



V. V. Zhirnov, R. K. Cavin, S. Menzel, E. Linn, S. Schmelzer, D. Bräuhaus, C. Schindler and R. Waser, “**Memory Devices: Energy-Space-Time Trade-offs**”, *Proc. IEEE* 98 (2010) 2185

In collaboration with RWTH Aachen Univ / Jülich Res. Ctr.

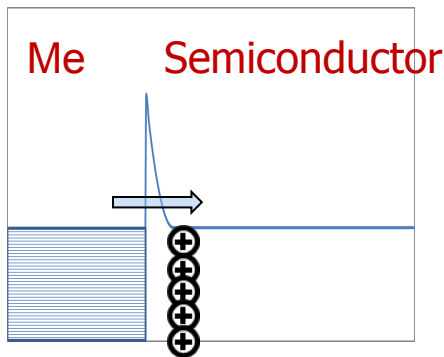
V. V. Zhirnov, R. Meade, R. K. Cavin, and G. Sandhu, “**Scaling Limits of Resistive Memories**”, *Nanotechnology* 22 (2011) 254027

V. V. Zhirnov and G. Sandhu, , "Scaling limits of nanoionic devices“, in *Resistive Switching*, D. Ielmini, R. Waser, ed., Wiley-VCH, (2014).

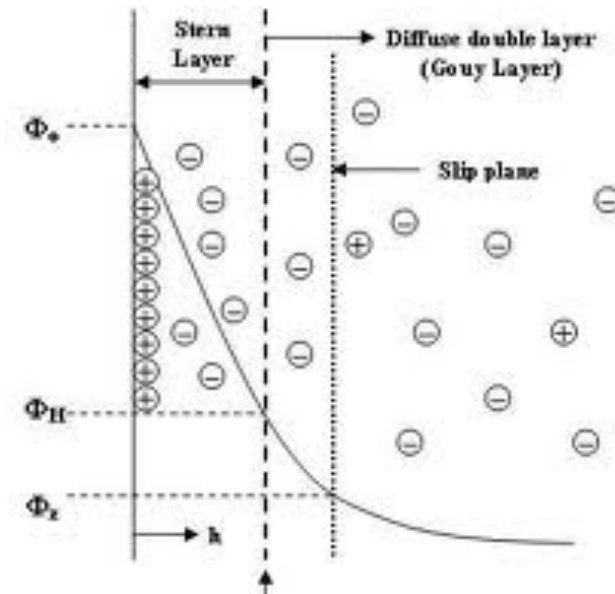
In collaboration with Micron Technology, Inc.

Memristors using Liquid Semiconductors' - Electrolytes

The formation of the electrical double-layer at metal-electrolyte interfaces is governed by similar physics as that for the depletion layer metal-semiconductor interfaces



W~5-10nm



W~0.5-1 nm

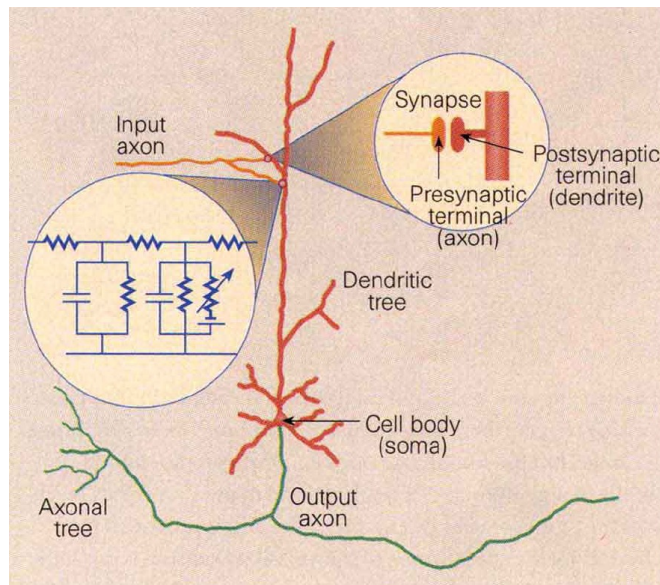
Sub 5nm 'repairable' devices, better heat removal etc.

What next? Ions in liquid electrolytes?

Ions in liquid electrolytes play an important role in biological information processors such as the brain

In the human brain, the distribution of **Ca** ions in dendrites may represent a crucial variable for processing and storing information.

Ca ions enter the dendrites through voltage-gated channels in a membrane, and this leads to rapid local modulations of calcium concentration within dendritic tree



Based on the brain analogy, the binary state can be realized by a single ion that can be moved to one of two defined positions, separated by a membrane (the barrier) with voltage-controlled conductance

Ions are heavy, but brain seems to use them efficiently!

Emerging Technology: Fluid nanoelectronics?

(Stuart Parkin, IBM)

- Fluid nanoelectronics utilizing liquid media may offer a new promising path to replace the foundation of today's computing technologies
 - Why IBM Made a Liquid Transistor - MIT Technology Review, <http://www.technologyreview.com/news/512721/why-ibm-made-a-liquid-transistor/>
 - NY Times: I.B.M. Research Points to Circuits That Mimic the Brain's Design, <http://bits.blogs.nytimes.com/2013/03/21/i-b-m-research-points-to-circuits-that-mimic-the-brains-design/>
- Examples include nanoionic devices based on electrolyte-filled nanochannels
 - DNA memory
 - protonic transistors, etc.
- Such structures might be used to make an atom-based binary switch scalable to ~ 1 nm or below
 - Fluid nanoelectronic systems could be reconfigurable, with individual elements strung together to create wires and circuits that could be reprogrammed
- Although it is at a very early stage, fluid nanoelectronics could someday allow for very powerful and energy-efficient computing



Way Beyond Moore: Information Processing By Nature

- 1) Living cell as an *in carbo* information processor
- 2) Information content of a material system/living cell
- 3) Essential parameters of an *in carbo* processor: Logic and Memory hardware
- 4) *In silico* vs. *in carbo* information processors: A comparison

V. V. Zhirnov and R. K. Cavin, "Microsystems for Bioelectronics" (Elsevier 2015)

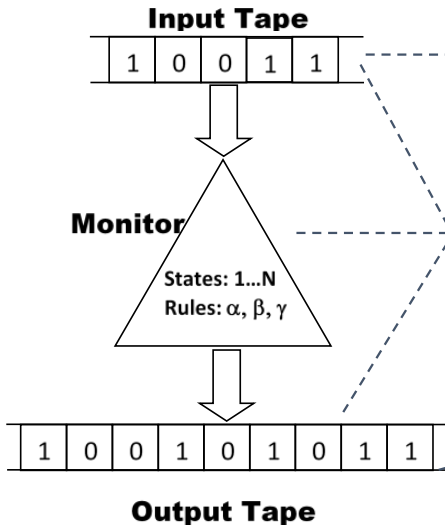
R. K. Cavin, P. Lugli and V. V. Zhirnov, "Science and Engineering Beyond Moore's Law", *Proc. IEEE* 100 (2012) 1720-1749

In collaboration with Technische Universität München

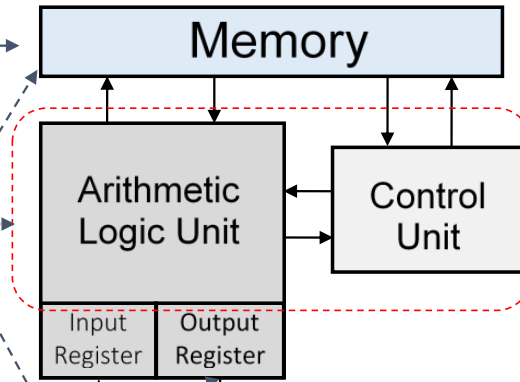


Abstract Information Processors

Turing Machine



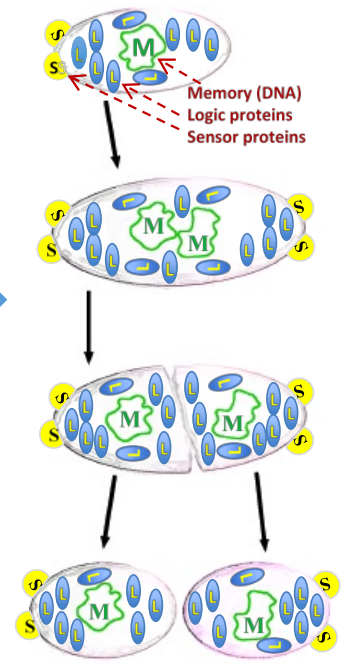
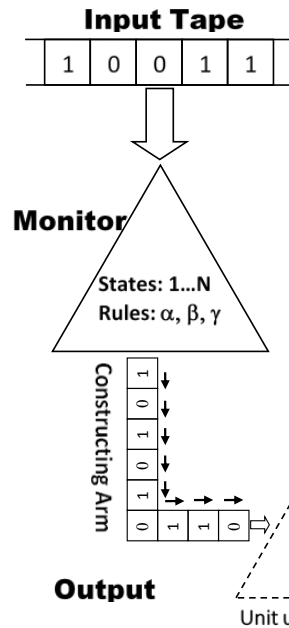
General-purpose Computer



Consider a computer with the task of controlling the assembly of a structure from building blocks



~500 "raw" bit transitions per useful bit



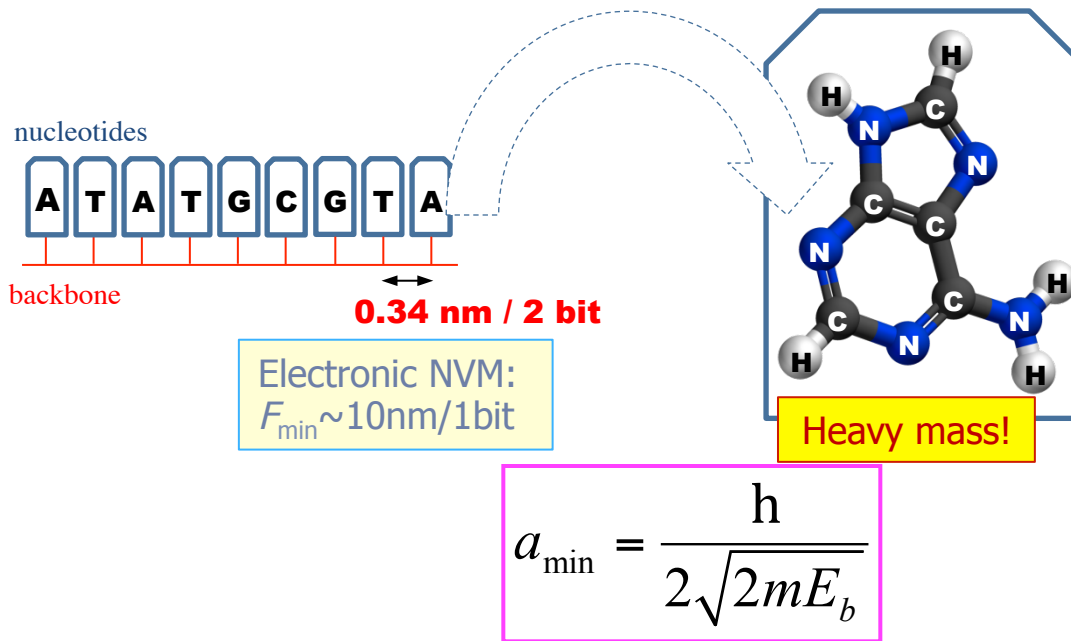
von Neumann Universal Constructor

R. Cavin, W. Joyner, and T. Noll, **Chapter 22:** *Performance Estimates for Microprocessors: at Technology Limits and in Practice*, in: **Nanoelectronics and Information Technology**, by R. Waser (Ed.) (Wiley 2012)



Memory Hardware

- All data about structure and operation of a living cell are stored in the long DNA molecule
 - Nonvolatile memory
- DNA coding uses a **base-4** (quaternary) system
 - The information is encoded digitally by using four different molecular fragments, to represent a state: adenine (A), cytosine (C), guanine (G), and thymine (T).



DNA is NOT a read-only memory

DNA memory operations

READ

- Multi-access capability by distinct computing units

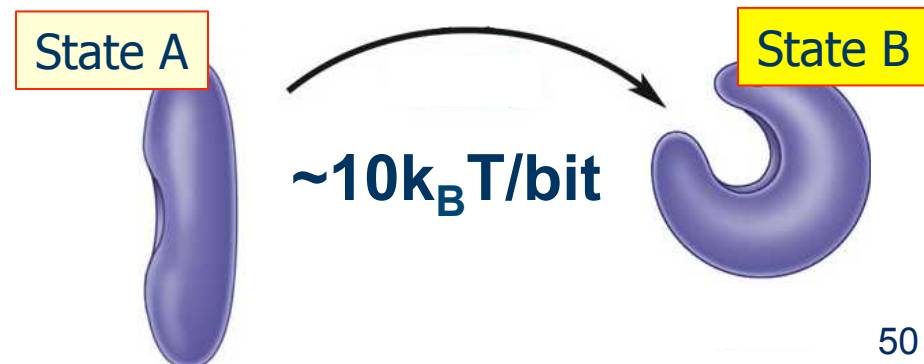
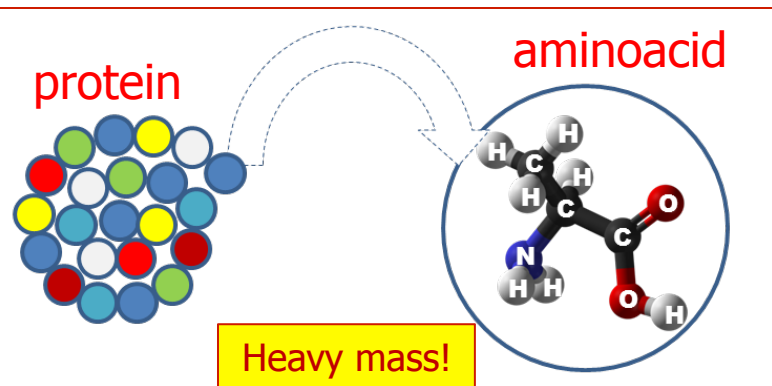
WRITE

Vertical gene transfer - exact copying of the parental DNA

Lateral (horizontal) gene transfer :

- (1) direct uptake ('swallowing') of a naked DNA by a cell,
- (2) by a virus,
- (3) by direct physical contact between two cells.

- Many proteins in cells have as their primary function the transfer and processing of information
 - are regarded as logic elements of the in-carbo processor
 - the proportion of components devoted to computational networks increases with the complexity of the cell, and are absolutely dominant in humans
- Proteins can alter their 3D structural shapes (*conformation*) in response to external stimuli,
 - different conformations can represent different logic states.
 - These *nanomechanical* changes form a state variable – **conformon**
 - Different *nanomechanical* conformations of these protein devices are recognized by other elements of the in-carbo cell circuit by a process based on *selective affinity* of certain biomolecules with given conformational states (e.g. electrostatic attraction)





Information Content of Living Cells: An upper bound estimate

Element	% of dry weight	m, kg	N_{at}
C	50	2×10^{-16}	8×10^9
O	20	6×10^{-17}	2×10^9
N	14	4×10^{-17}	2×10^9
H	8	2×10^{-17}	1×10^{10}
P	3	9×10^{-18}	2×10^8
S	1	3×10^{-18}	6×10^7
K	1	3×10^{-18}	5×10^7
Mg	0.5	2×10^{-18}	4×10^7
Ca	0.5	2×10^{-18}	2×10^7
Fe	0.2	6×10^{-19}	6×10^6
Total	99.2%	3×10^{-16}	3×10^{10}

$$I_M = K(\log_2 N + 3n)$$

$$I_{cell} \sim 3 \cdot 10^{10} \cdot (\log_2 10 + 3 \cdot 32) \sim 3 \cdot 10^{12} \text{ bit}$$

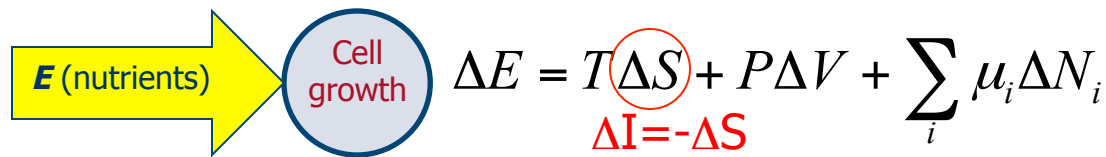
an upper bound on the information content that must be processed to assemble a new cell.

a more accurate estimate: $\langle I \rangle = \sum_i^N p_i I_i(p_i) = \sum_i^N -C p_i \log p_i = -C \sum_i^N p_i \log p_i$

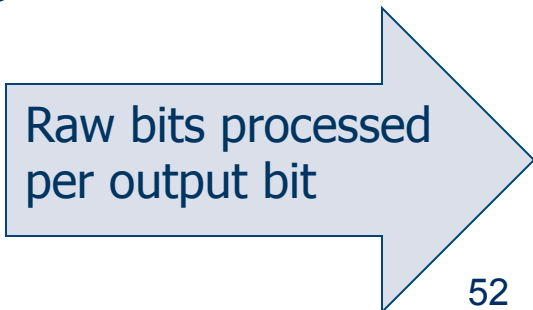


Information Content of Bacterial Cells: Theory vs. Experimental Estimates

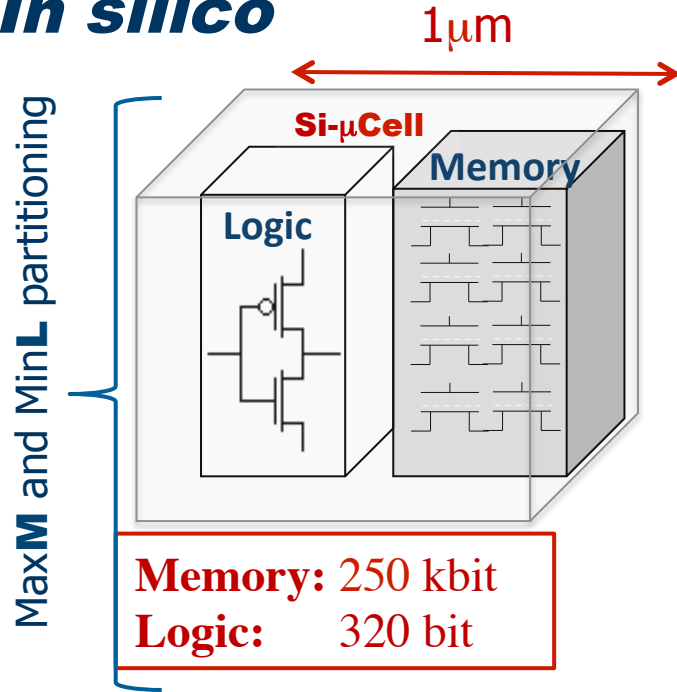
- An upper bound estimate: $\sim 3 \times 10^{12}$ bits (this work)
- Experimental estimates: $10^{11} - 10^{13}$ bits
 - Experimental estimates of the information content of living cells were made based on *microcalorimetric measurements*.
 - It has been concluded that the major consumption of energy during a cell's reproduction cycle arises from the correct placement of molecules within the cell. *W. W. Forrest, "Entropy of microbial growth", Nature 225 (1970) 1165-1166*



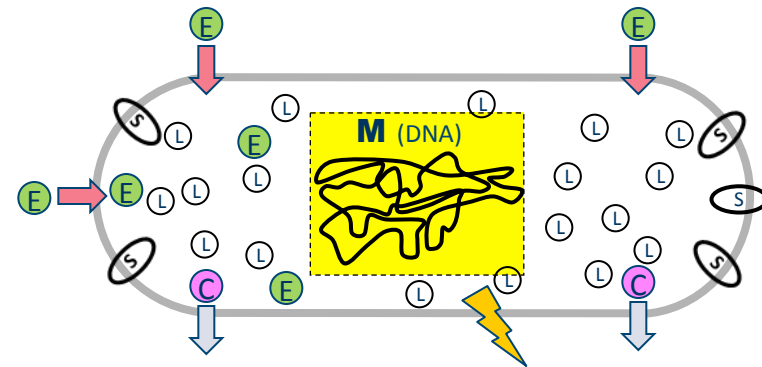
- In the following, the conservative edge of the estimated range is used: $\sim 10^{11}$ bits
 - (the number of *output bits*)



In silico



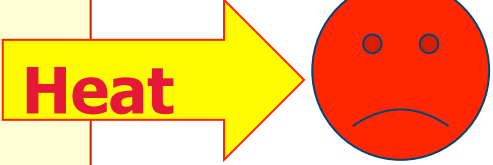
In carbo



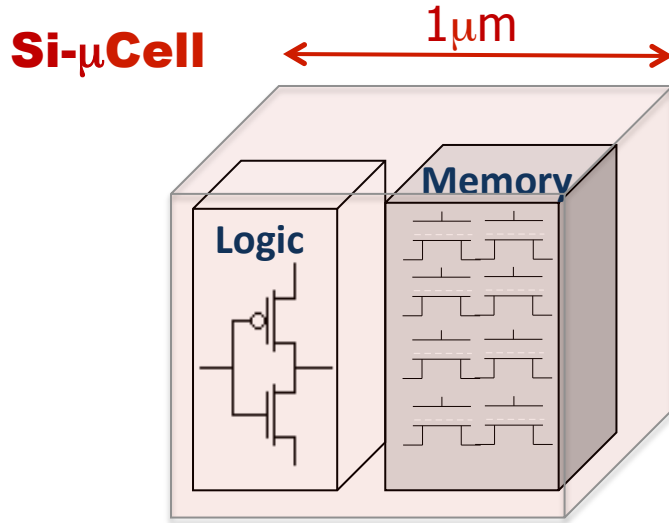
Computational Task: **10^{11} output bits**
Task Time: **2400s**

Computational Task: **10^{11} output bits**
($\sim 5 \times 10^{13}$ raw bits)
Task Time: **2400 s**
Cycles per output bit: **3**
Required cycle time: **8 ns**

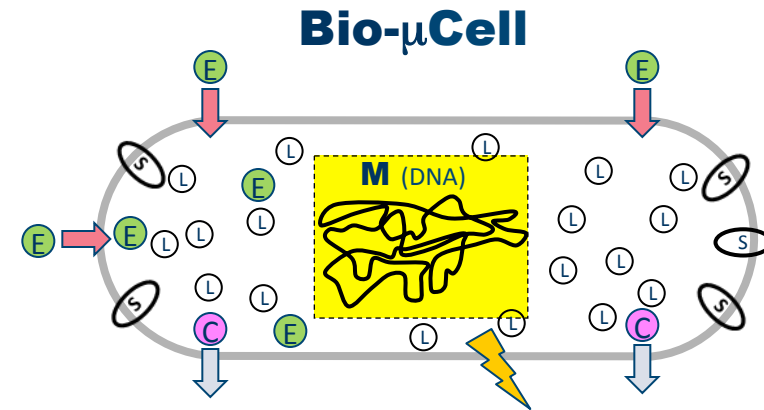
Matching the bio- μ Cell



In-Silico versus In-Carbo



Memory:	$\sim 10^5$ bit
Logic:	$\sim 300\text{--}100,000$ bit
Power:	$\sim 10^{-7}$ W
Heat:	~ 1 W/cm ²
Total energy/task*:	$\sim 10^{-3}$ J
Task time*:	50,000 s \sim 14h



Memory:	10^7 bit
Logic:	$>10^6$ bit
Power:	10^{-13} W
Heat:	10^{-6} W/cm ²
Total energy/task*:	10^{-9} J
Task time*:	2400s=40min

*Equivalent to 10^{11} output bits

A Si- μ Cell fundamentally cannot match the bio- μ Cell in the operational energy.

Given:

Memory:

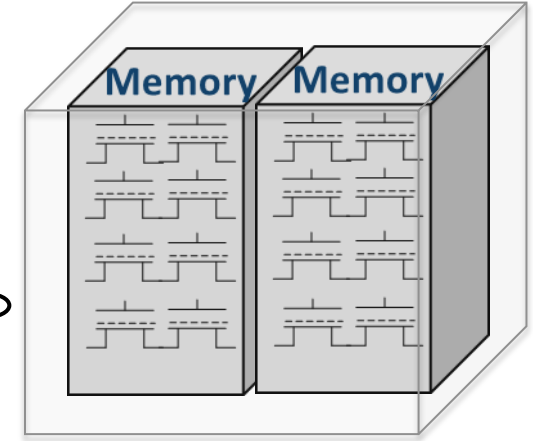
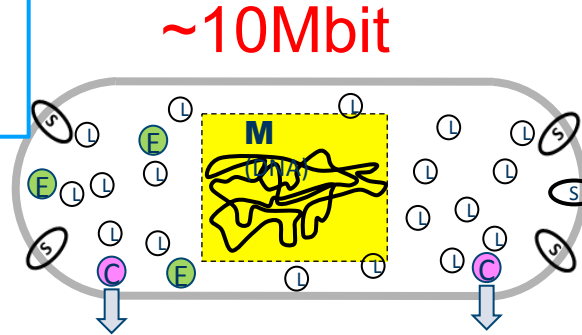
9.6 Mbit

Power:

10^{-13} W

Task time*:

2400s=40min



$N \sim 100$ kbit

$E \sim 10^{-14}$ J

Simplifying Assumption:

The entire DNA information content is read and written at least once during one cell division cycle

Characteristic access time per bit: $t_{bit} \sim \frac{2400}{2 \cdot 9.6 \cdot 10^6} \sim 100 \mu s$

Characteristic energy per bit (system-level): $E < \frac{10^{-13} W \cdot 2400 s}{2 \cdot 9.6 \cdot 10^6} = 2.5 \cdot 10^{-17} \frac{J}{bit}$

Example I: DNA Memory

ScienceExpress

16 August 2012

Next-Generation Digital Information Storage in DNA

George M. Church,^{1,2} Yuan Gao,³ Sriram Kosuri^{1,2*}

¹Department of Genetics, Harvard Medical School, Boston, MA 02115, USA. ²Wyss Institute for Biologically Inspired Engineering, Boston, MA 02115, USA. ³Department of Biomedical Engineering, Johns Hopkins University, Baltimore, MD 21205, USA.

*To whom correspondence should be addressed. E-mail: sri.kosuri@wyss.harvard.edu

Researchers **stored an entire genetics textbook** in less than a picogram of DNA — one trillionth of a gram — an advance that could revolutionize our ability to save data.

5.27×10^6 bit

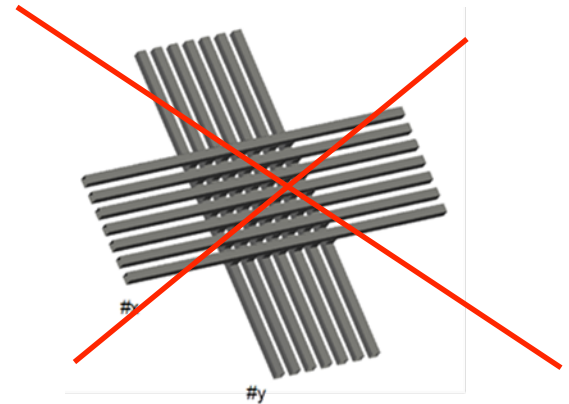


DNA memory can be stable ~ 100y+

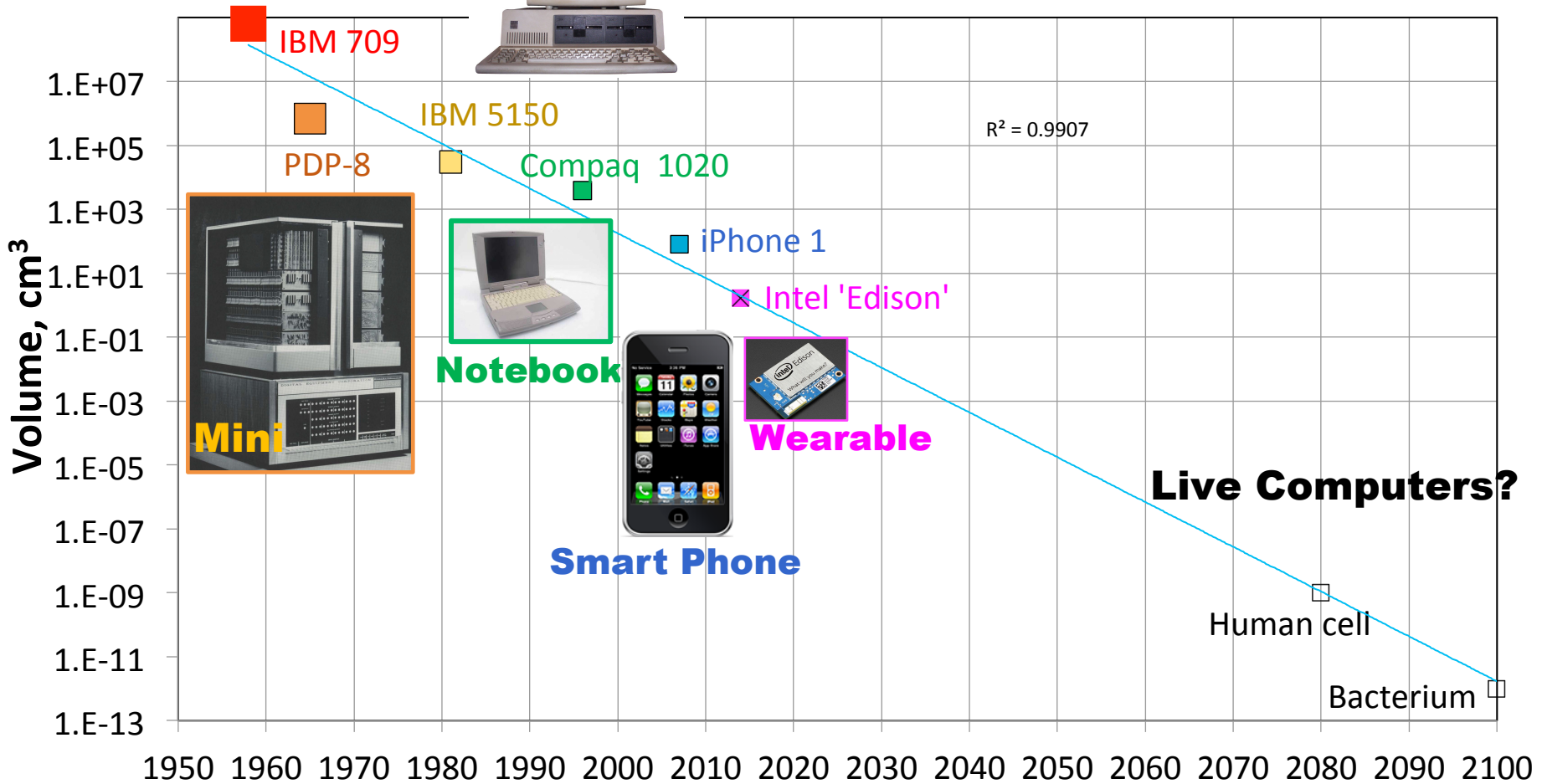
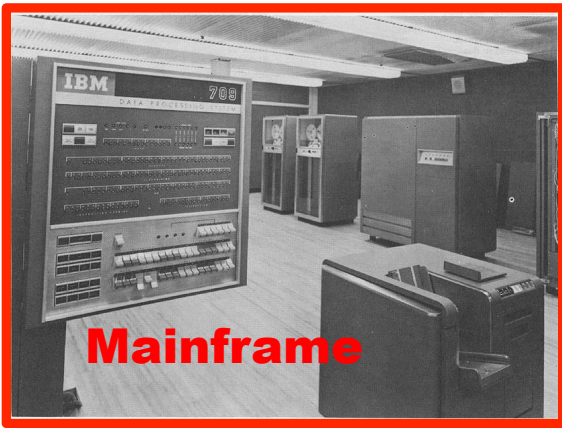
HARDWARE: Agilent Oligo Library Synthesis microarray platform

- Agilent Technologies, a spin-off of Hewlett-Packard (1999), originally a semiconductor company, which became now a global company offering products & services in communications, electronics, semiconductor, test and measurement, life sciences and chemical analysis industries.
 - Example of a successful convergence of semiconductor and bio industries

- Heavier mass of information carrier
 - Molecules instead electrons
 - Smaller device size
- Array-less memory organization
 - energy minimization
- Utilized ambient thermal energy
 - For *in silico* systems thermal energy is an enemy!
- Flexible/on-demand connections/routing
 - *In silico*: most energy is consumed by interconnect

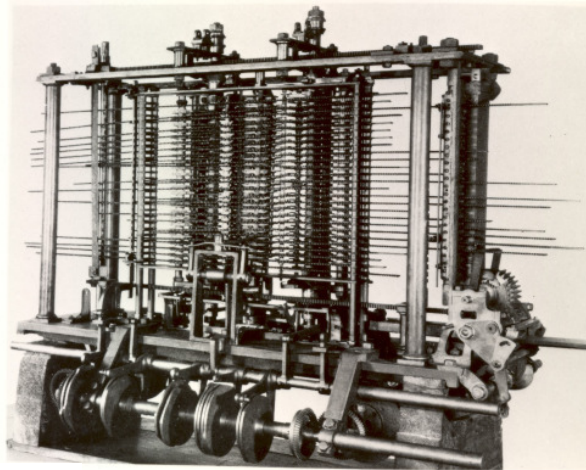
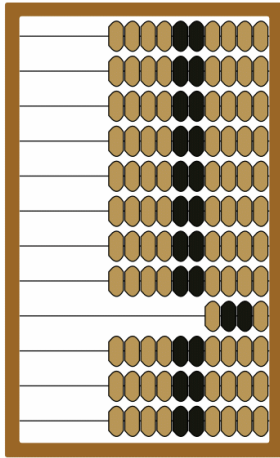


Computing system Scaling (Bell's Law)



- Basic physics enables key insights into the limits of component and system scaling
- Extreme component scaling holds the promise of highly functional micron-scale systems
- Micron-scale energy sources are key to extreme microsystems
 - Design space is bounded by the limits of energy sources
- Communication energy/volume expenditures is most costly activity – should therefore maximize “system intelligence”
- We suggest that inspiration for future ultra-low energy computing architectures can be derived from organic systems, i.e., at the intersection of chemistry, biology, and information processing

Do all computing engines have a common soul?



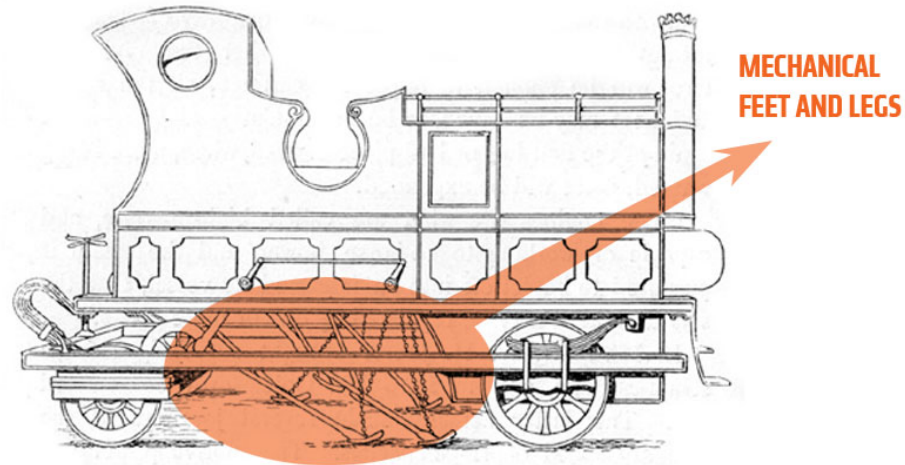
Mechanical

Chemical???



An Early Steam Car Used Mechanical Feet To Move

In 1824, David Gordon designed and built a three-wheeled, *six-legged* steam carriage.



He emulated a mode of transportation he knew worked very well horses



MIPS as an indicator of hardware performance

P. Hilbert and M. Lopez, “The world’s technological capacity to store, communicate and compute information”, Science 332 (2011) 60

- Measuring the computational power of digital devices is not an easy task
 - Their characteristics are multidimensional
- The final choice of our unit of measurements was determined principally by the availability of relevant and consistent statistics, more than their robustness
- Dhrystone VAX MIPS as units of measurements
 - Extensive databases available
 - Conversion from SPEC to Dhrystone MIPS established
 - Conversion from FLOPS to Dhrystone MIPS established

System Constraint on Minimum Energy per Bit



$$\Pi_{sys} = (1 - \Pi_{err})^N$$

The probability that all N switches in a circuit work correctly

$$\Pi_{sys} > \Pi_{crit} \quad \text{e.g., } \begin{matrix} \nearrow 0.5 \\ \searrow 0.99 \end{matrix}$$

lower boundary

a "reasonable" boundary

$$\Pi_{err} = 1 - \Pi_{crit}^{\frac{1}{N}}$$

$$\Pi_{err} = f(E_b)$$

$$E_{b_{min}} = f(N)$$

$$N_{max} \sim \frac{1}{a^2}$$



Boltzmann

Heisenberg

$$\Pi_{err} = \exp\left(-\frac{E_b}{kT}\right) + \exp\left(-\frac{2\sqrt{2m}}{\hbar} a\sqrt{E_b}\right) - \exp\left(-\frac{\hbar E_b + 2akT\sqrt{2mE_b}}{\hbar kT}\right)$$

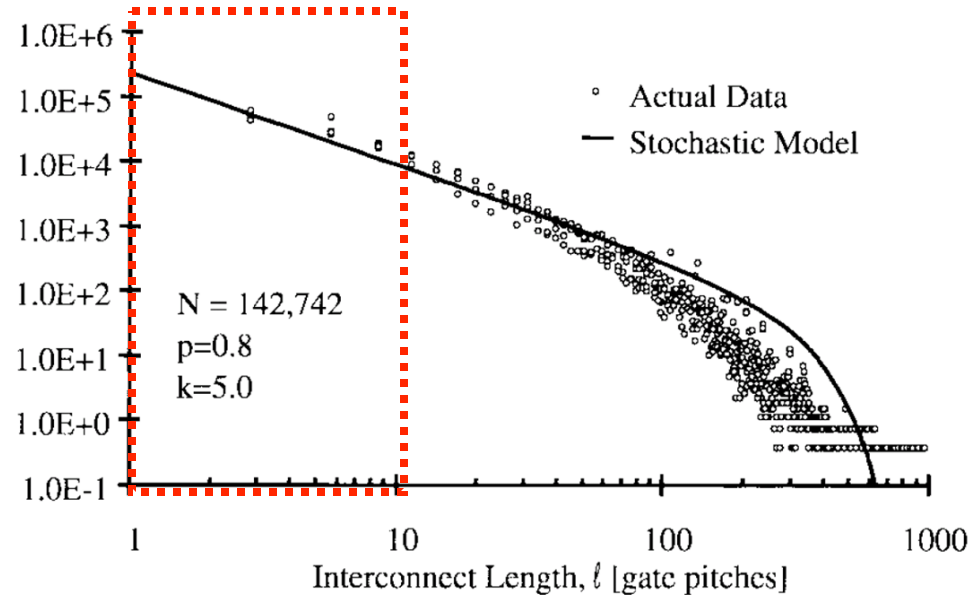
SRC[®] Long Interconnects

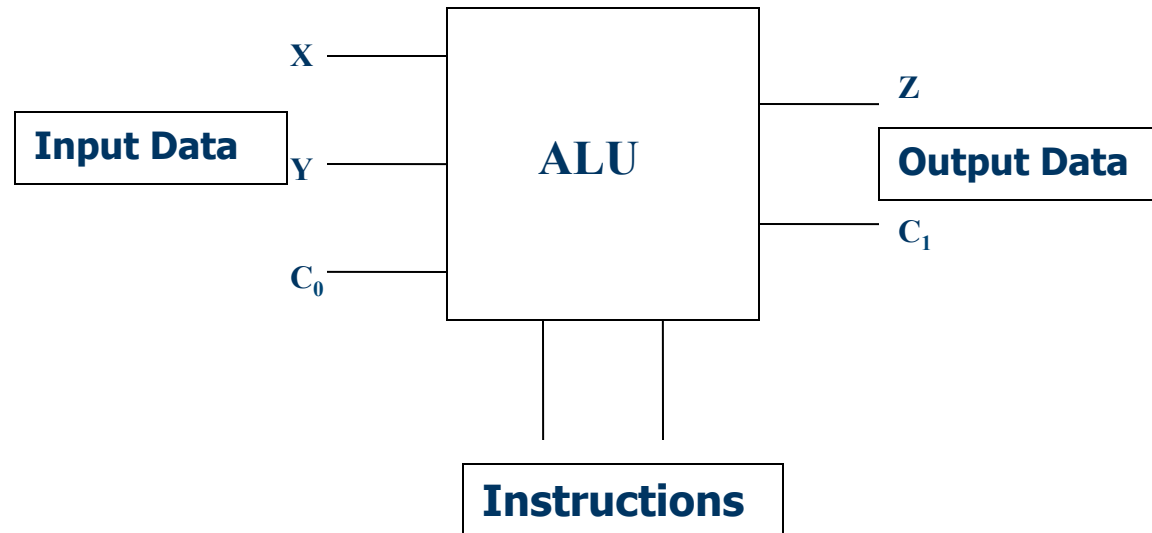
- In interconnects, the number of electrons needs to be sufficient to guarantee successful communication between binary switches

$$n=2 \quad L=100a$$

$$\Pi_n = \left(1 - \left(1 - \frac{a}{L} \right)^N \right)^n$$

N electrons	Operational reliability	
121	50%	$E \sim 120k_B T$
198	75%	$E \sim 200k_B T$
487	99%	$E \sim 500k_B T$





The minimal ALU does $2^2=4$ operations on two 1-bit X and Y:

Operation 1: X AND Y

Operation 2: X OR Y

Operation 3: (X+Y)

Operation 4: (X+(NOT Y))

Supports functionally complete set of logic and arithmetic operations